

M.2 NVMe SSD Specification

(PM9A3)

Datasheet

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Revision History

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Part Number	Capacity	LBA (512B Bytes size)
MZ1L2960HCJR-00A07	960GB	1,875,385,008
MZ1L21T9HCLS-00A07	1920GB	3,750,748,848
MZ1L23T8HBLA-00A07	3840GB	7,501,476,528

FEATURES

- PCI Express Gen4
 - Single port x4 lanes
- Compliant with PCI Express Base Specification Rev. 4.0
- Compliant with NVM Express Specification Rev. 1.4
- Enhanced Power-Loss Data Protection
- End-to-End Data Protection
- Support SSD Enhanced S.M.A.R.T. Feature Set
- Hardware based AES-XTS 256-bit Encryption Engine
- Static and Dynamic Wear Leveling
- RoHS / Halogen-Free Compliant
- TCG Opal 2.0 Compliant

DRIVE CONFIGURATION

- Form Factor M.2
- Interface PCI Express Gen4 x4
- Bytes per Sector 512(default), 4096 Bytes

PERFORMANCE SPECIFICATIONS²⁾**Gen3**

- Data Transfer Rate (128KB data size)
 - Sequential Read Up to 3500 MB/s³⁾
 - Sequential Write Up to 2000 MB/s
- Data I/O Speed (4KB data size, Sustained)
 - Random Read Up to 800K IOPS
 - Random Write Up to 85K KIOPS

Gen4**Gen4**

- Data Transfer Rate (128KB data size)
 - Sequential Read Up to 5500 MB/s³⁾
 - Sequential Write Up to 2000 MB/s
- Data I/O Speed (4KB data size, Sustained)
 - Random Read Up to 800K IOPS
 - Random Write Up to 85K KIOPS
- Latency (Sustained workload)
 - Random Read/ Write (typical)⁴⁾ 75/30 us
 - Sequential Read/ Write (typical)⁵⁾ 20/20 us
 - Drive Ready Time (typical) 5s

RELIABILITY SPECIFICATIONS

- Uncorrectable Bit Error Rate 1 sector per 10^{17} bits read
- MTBF 2,000,000 hours
- Component Design Life 5 years
- Endurance
 - 3840/1920/960GB 1DWPD
- TBW (@4KB Random Write)
 - 3840GB 7008 TB
 - 1920GB 3504 TB
 - 960GB 1752TB
- Data Retention 3 months

ENVIRONMENTAL SPECIFICATIONS

- Temperature, Case (T_c ⁶⁾)
 - Operating 0 ~ 70 °C
 - Non-operating -40 ~ 85 °C
- Humidity (non-condensing) 5 ~ 95%
- Linear Shock (0.5ms duration with 1/2 sine wave)
 - Non-operating 1,500 G
- Vibration
 - Non-operating (10 ~ 2,000 Hz, Sinusoidal) 20 G

POWER REQUIREMENTS

- Supply Voltage / Tolerance 3.3V±5 %
- Active⁷⁾ (max. RMS) 8.2W
- Idle (typ.) 2.5W

PHYSICAL DIMENSION

- Width 22.00 ± 0.15 mm
- Length 110.00 ± 0.15 mm
- Thickness 3.80 ± 0.18 mmT
- Weight Up to 20 g

OPERATING SYSTEMS

- RHEL 7.6/8.2
- CentOS 7.6/8.2
- Ubuntu 18.10/20.04
- Windows Server 2016/2019

NOTE: Specifications are subject to change without notice.

1) 1MB = 1,000,000 Bytes, 1GB = 1,000,000,000 Bytes, unformatted Capacity. User accessible capacity may vary depending on operating environment and formatting.

2) Based on PCI Express Gen3 x4, Random performance measured using FIO 2.1.3 in CentOS6(Kernel 3.14) with 4KB (4,096 bytes) of data transfer size in queue depth 32 by 4 workers and Sequential performance with 128KB (131,072 bytes) of data transfer size in queue depth 32 by 1 worker. Actual performance may vary depending on use conditions and environment.

3) 1 MB/sec = 1,000,000 bytes/sec was used in sequential performance.

4) The random latency is measured by using FIO 2.1.3 in Linux RHEL 6.6(Kernel 3.14.29) and 4KB (4,096 bytes) transfer size with queue depth 1 by 1 worker.

5) The Sequential latency is measured by using FIO 2.1.3 in CentOS6(Kernel 3.14) and 4KB (4,096 bytes) transfer size with queue depth 1 by 1 worker.

6) T_c is defined as the Max surface temperature of NAND packages. Sufficient cooling airflow or effective heat-dissipation add-on(i.e. heat sink or heat spreader) are recommended to be operated properly on heavier workloads within device operating temperature.

7) Active power is measured using IOmeter2006 on Windows Server 2012.

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1.0 INTRODUCTION

1.1 General Description

This document describes the specifications of the Samsung SSD PM9A3, which is a native-PCIe SSD for enterprise application.

The Samsung SSD PM9A3 presents outstanding performance with instant responsiveness to the host system, by applying the Peripheral Component Interconnect Express (PCIe) 3.0 interface standard, as well as highly efficient Non-Volatile Memory Express (NVMe) Protocol.

The Samsung SSD PM9A3 delivers wide bandwidth of up to 3,500MB/s for sequential read speed and up to 2,100MB/s for sequential write speed under up to 8.2W power. With the help of Toggle 2.0 NAND Flash interface, the Samsung SSD PM9A3 delivers random performance of up to 800KIOPS for random 4KB read and up to 85KIOPS for random 4KB write in the sustained state.

By combining the enhanced reliability Samsung NAND Flash memory silicon with NAND Flash management technologies, the Samsung SSD PM9A3 delivers the extended endurance of up to 1.3 drive writes per day over 3 years, which is suitable for enterprise applications, in M.2 form factor line ups: 960GB and 1920GB

In addition, the Samsung SSD PM9A3 supports Power Loss Protection (PLP). PLP solution can guarantee that data issued by the host system are written to the storage media without any loss in the event of sudden power off or sudden power failure.

1.2 Product List

[Table 1] Product List

Type	Capacity	Part Number
M.2 ¹⁾	960GB	MZ1L2960HCJR-00A07
	1920GB	MZ1L21T9HCLS-00A07
	3840GB	MZ1L23T8HBLA-00A07

NOTE:

1) $22.00 \pm 0.15 \times 110.00 \pm 0.15 \times 3.80 \pm 0.18$

1.3 Ordering Information

M Z X X X X X X X X X - X X X X X

1 2 3 4 5 6 7 8 9 10 11 12 13 14 15 16 17 18

1. Memory (M)

2. Module Classification

Z: SSD

3. Form Factor

1: PCIe M.2 (22*110)

4. Line-Up

L: SV (VNAND 3bit MLC)

5. SSD CTRL

2: Elpis, S.LSI

6~8. SSD Density

960: 960GB

1T9: 1920GB

3T8: 3840GB

9. NAND PKG + NAND Voltage

H: BGA (LF,HF)

10. Flash Generation

C : 4th Generation

11~12. NAND Density

JR : 2T ODP 2CE (FBI)

LS : 4T HDP 2CE(FBI)

LA : 8T HDP 2CE(FBI)

13. "-"

14. Default

"0"

15. HW revision

0: No revision

16. Packaging type

A: Retail Packaging

17~18. Customer

07: General

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2.0 PRODUCT SPECIFICATIONS

2.1 Capacity

[Table 2] User Capacity and Addressable Sectors

Capacity ²⁾	Max LBA ³⁾
960GB	1,875,385,008
1920GB	3,750,748,848
3840GB	7,501,476,528

NOTE:

1) Gigabyte (GB) = 1,000,000,000 Bytes, 1 Sector = 512Bytes

2) Capacity shown in Table 2 represents the total usable capacity of the SSD which may be less than the total physical capacity. A certain area in physical capacity, not in the area shown to the user, might be used for the purpose of NAND flash management.

3) Max. LBA shown in Table 2 represents the total user addressable sectors in LBA mode and calculated by IDEMA rule.

2.2 Performance

[Table 3] Sustained Random Read/Write Performance (IOPS)

Maximum Performance ¹⁾	Unit	Gen3			Gen4		
		960GB	1920GB	3840GB	960GB	1920GB	3840GB
Random 4KB Read (Up to)	IOPS	550K	800K	800K	550K	800K	800K
Random 4KB Write (Up to)	IOPS	60K	85K	85K	60K	85K	85K

NOTE:

1) Random performance in Table 3 was measured by using FIO 2.7 in Linux Gen3: CentOS6(kernel 3.14) with 4KB (4,096 bytes) of data transfer size in Queue Depth=32 by 4 workers. Measurements were performed on a full Logical Block Address (LBA) span of the drive in sustained state. The actual performance may vary depending on use conditions and environment.

[Table 4] Sequential Read/Write Performance

Maximum Performance ¹⁾	Unit	Gen3			Gen4		
		960GB	1920GB	3840GB	960GB	1920GB	3840GB
Sequential 128KB Read (Up to)	MB/s	3500	3500	3500	5000	5500	5500
Sequential 128KB Write (Up to)	MB/s	1400	2000	2000	1400	2000	2000

NOTE:

1) Sequential performance in Table 4 was measured by using FIO 2.7 in Linux Gen3: CentOS6(kernel 3.14) with 128KB (131,072 bytes) of data transfer size in Queue Depth=32 by 1 worker.

[Table 5] IOPS Consistency

Maximum Performance ¹⁾	960GB	1920GB	3840GB
Random Read (4 KB)	95%	95%	95%
Random Write (4 KB)	95%	95%	95%

NOTE:

1) IOPS consistency measured using FIO with queue depth 32.

2) IOPS Consistency (%) = (99.9% IOPS) / (Average IOPS) x 100.

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2.3 Latency

[Table 6] Latency¹⁾ (sustained state)

Queue Depth = 1	Unit	960GB	1920GB	3840GB
Random Read/Write ²⁾	us	75/30	75/30	75/30
Sequential Read/Write ³⁾	us	20/20	20/20	20/20
Drive Ready Time ⁴⁾	sec	5	5	5

NOTE:

1) Typical values.

2) The random latency is measured by using FIO 2.7 in Linux Gen3: CentOS6(kernel 3.14) and 4KB transfer size with queue depth 1 by 1 worker.

3) The sequential latency is measured by using FIO 2.7 in Linux Gen3: CentOS6(kernel 3.14) and 4KB transfer size with queue depth 1 by 1 worker.

4) The maximum taking time to be ready for receiving commands after power-up (CSTS.Ready=1). It is expected that I/O commands may not be completed at this point.

2.4 Quality of Service (QoS)

[Table 7] Quality of Service (QoS)

Quality of Service (99%)	Unit	960GB	1920GB	3840GB
Read(4KB, QD=1)	ms	0.1	0.1	0.1
Read(4KB, QD=32)	ms	0.5	0.25	0.25
Write(4KB, QD=1)	ms	0.06	0.03	0.03
Write(4KB, QD=32)	ms	0.8	0.7	0.7

Quality of Service (99.99%)	Unit	960GB	1920GB	3840GB
Read(4KB, QD=1)	ms	0.15	0.15	0.15
Read(4KB, QD=32)	ms	0.6	0.5	0.5
Write(4KB, QD=1)	ms	0.06	0.04	0.04
Write(4KB, QD=32)	ms	0.8	0.7	0.7

NOTE:

1) QoS is measured using FIO 2.7 in CentOS6 (Linux kernel 3.14) with queue depth 1, 32 on 4KB random read and write.

2) QoS is measured as the maximum round-trip time taken for 99 and 99.99% of commands to host.

2.5 Power

The Samsung SSD PM9A3 is implemented in standardized M.2 form factor and gets primary 3.3V power from the host system. For 3.3V, the allowable voltage tolerance and noise level in SSD are described in chapter 2.5.1, the power consumption in 2.5.2 and the inrush current in 2.5.3.

2.5.1 Maximum Voltage Ratings (3.3V)

[Table 8] Allowable Voltage Tolerance¹⁾

Operating Voltage	960GB	1920GB	3840GB
3.3V		5%	
3.3V Noise level	DC to 100Khz : 300 mVp-p Max 100Khz to 20Mhz : 50 mVp-p Max		
3.3V Min Off time		10ms	

NOTE:

1) The components inside SSD were designed to endure the range of voltage fluctuations, which might be induced by the host system, in Table 6.

2.5.2 Power Consumption (3.3V)

In enterprise server and storage system, the Samsung SSD PM9A3 is designed for the specific usage, which means that SSD will be always operated by the host system during the entire life. Hence, the Samsung SSD PM9A3 does not manage any low power modes except for the Active/Idle and Off mode.

[Table 9] Power Consumption (3.3V Supply Voltage)¹⁾

Power Mode	960GB	1920GB	3840GB
Active ²⁾	Read	7.5W	8.0W
	Write	6.5W	8.2W
Idle ³⁾	2.5W	2.5W	2.5W

NOTE:

1) Power consumption was measured in the 3.3V power pins of the connector plug in SSD. The active and idle power is defined as the highest averaged power value, which is the maximum RMS average value over 100 ms duration.

2) The measurement condition for active power is assumed for Maximum power between sequential or random performancein PCIe Gen4.

3) The idle state is defined as the state that the host system can issue any commands into SSD at any time.

2.5.3 Inrush Current

[Table 10] Inrush Current

Inrush Current	960GB	1920GB	3840GB
3.3V		1A	

2.5.4 Power Loss Protection

By using internal back-up power technology, the Samsung SSD PM9A3 supports power loss protection (PLP) feature to guarantee the reliability of data requested by the host system. When power is unpredictably lost, SSD can detect automatically this abnormal situation and transfer all user data and meta-data cached in DRAM into the Flash media during any SSD operations.

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2.6 Reliability

The reliability specification of the Samsung SSD PM9A3 follows JEDEC standard, which are included in JESD218A and JESD219A documents

2.6.1 Mean Time Between Failures

By definition, Mean Time between Failures (MTBF) is the estimated time between failures occurring during SSD operation.

[Table 11] MTBF Specifications

Parameter	960GB	1920GB	3840GB
MTBF		2,000,000 Hours	

2.6.2 Uncorrectable Bit Error Rate

By definition, Uncorrectable Bit Error Rate (UBER) is a metric for the rate of occurrence of data errors, equal to the number of data errors per bits read as specified in the JESD218 document of JEDEC standard.

[Table 12] UBER Specifications

Parameter	960GB	1920GB	3840GB
UBER		1 sector per 10^{17} bits read	

2.6.3 Data Retention

By definition, data retention is the expected time period for retaining data in the SSD at the maximum rated endurance in power-off state as specified in the JESD218 document of JEDEC standard.

[Table 13] Data Retention

Parameter	960GB	1920GB	3840GB
Data Retention ¹⁾		3 months	

NOTE:

1) Data retention was measured by assuming that SSD reaches the maximum rated endurance at 40C in power-off state.

2.6.4 Endurance

By definition, the endurance of SSD in enterprise application is defined as the maximum number of drive writes per day that can meet the requirements specified in the JESD218 document of JEDEC standard.

[Table 14] Drive Write Per Day (DWPD)

Parameter	960GB	1920GB	3840GB
DWPD		1 drive writes per day over 5years	

[Table 15] TBW (Tera Bytes Written) Specifications

Parameter	Unit	960GB	1920GB	3840GB
TBW	TB	1752	3504	7008

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2.7 Environmental Specification

2.7.1 Temperature

[Table 16] Temperature, Case (Tc¹⁾)

Parameter		960GB	1920GB	3840GB
Temperature ¹⁾	Operating	0 to 70°C		
	Non-operating	-40 to 85°C		

NOTE:

1) Tc is defined as the Max surface of NAND packages. Sufficient airflow is recommended to be operated properly on heavier workload within device operating temperature.

2.7.2 Dynamic Thermal Throttling

The dynamic thermal throttling (DTT) is implemented to prevent overheating. Table 17 shows the engaging and recovery temperature thresholds.

2.7.2.1 DTT table

[Table 17] Dynamic Thermal Throttling

Step	Engaging temperature ^{1),2)}	Dis-engaging temperature	Performance ³⁾
DTT1	77°C	76°C	<85%
DTT2	81°C	80°C	<50%
DTT3	83°C	82°C	<25%
Critical (DTT4)	85°C	84°C	<1%
Shut-down ⁴⁾	93°C	N/A	N/A
Warning Composite Temperature (WCTEMP)		77°C	
Critical Composite Temperature (CCTEMP)		85°C	

NOTE:

1) All temperatures are based on T_{composite} values.

2) Recovering to the previous step as the temperature falls.

3) Throttling levels could be varying with workloads

4) Hanged/Halted. Recovering after power cycle.

2.7.2.2 Tcomposite

The Tcomposite is defined by the correlation equations as the below.

$$T_{\text{composite}} = TS$$

where, TS means the temperature of reading in the thermal sensor on SSD.

2.7.3 Humidity

[Table 18] Humidity

Parameter		960GB	1920GB	3840GB
Humidity ¹⁾	Non-operating	5% to 95%		

NOTE:

1) Humidity is measured in non-condensing state.

2.7.4 Shock and Vibration

[Table 19] Shock and Vibration

Parameter		960GB	1920GB	3840GB
Shock ¹⁾	Non-operating	1,500 G		
Vibration ²⁾	Non-operating	20 G		

NOTE:

1) Test condition for shock: 0.5ms duration with half sine wave.

2) Test condition for vibration: 10Hz to 2000Hz.

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3.0 MECHANICAL SPECIFICATIONS

3.1 Physical Information

The physical case of the Samsung SSD PM9A3 in M.2 form factor follows the standardized dimensions defined by SSD Form Factor Work Group

[Table 20] Physical Dimensions and Weightnical Outline

Parameter	Unit	960GB	1920GB	3840GB
Width	mm		22.00 ± 0.15	
Length	mm		110.00 ± 0.15	
Thickness	mm		3.80 ± 0.18	
Weight	g		Up to 20.0g	

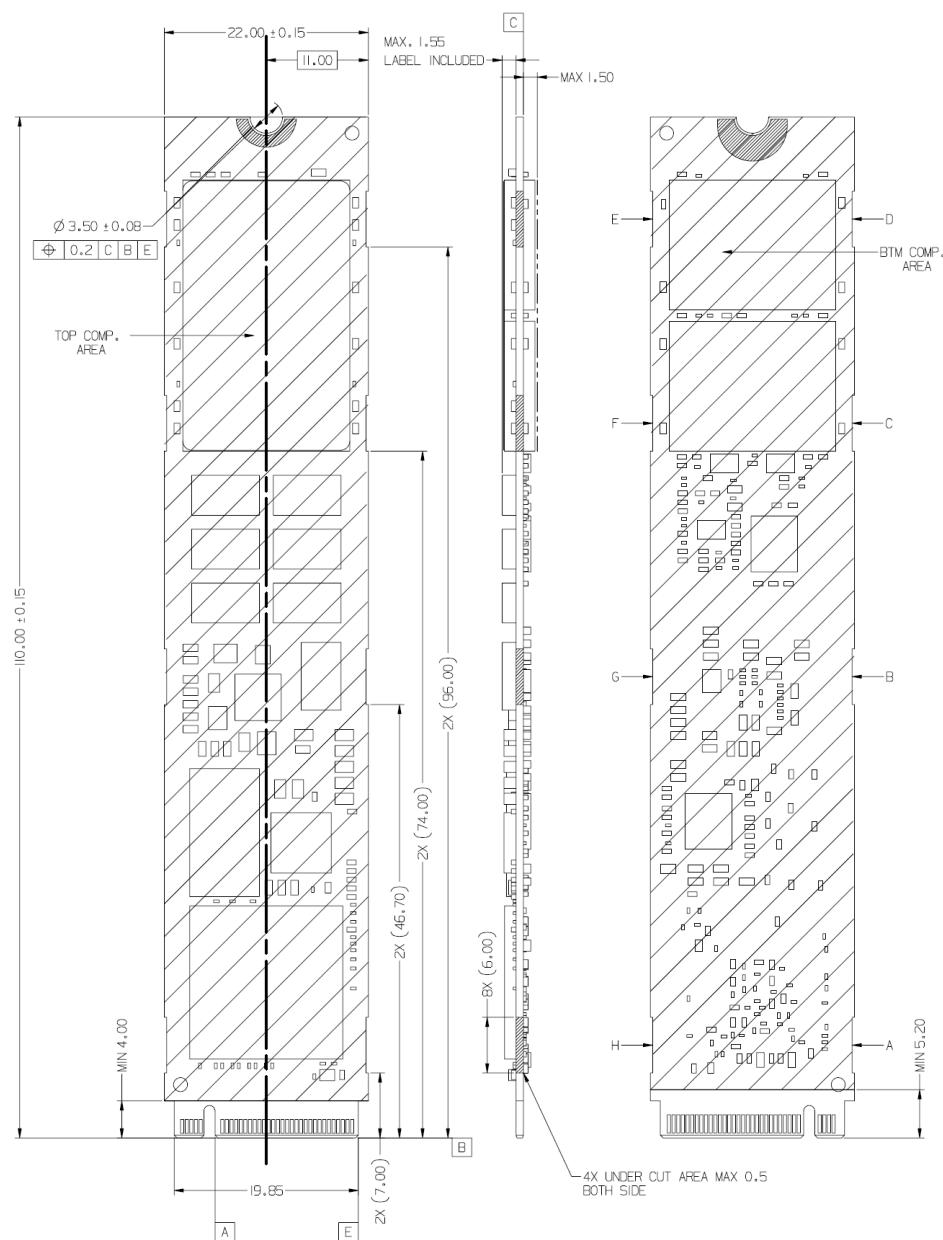


Figure 1. Mechanical Outline 1

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4.0 INTERFACE SPECIFICATION

4.1 Connector Dimensions

Drive Connector: FOXCONN

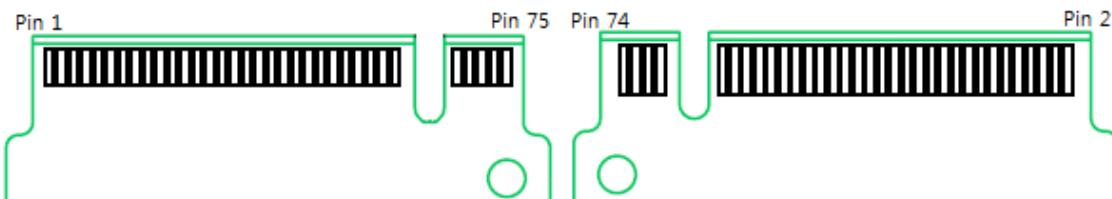


Figure 2. M.2 Signal and Power pins

4.2 Connector Pin Assignments

[Table 21] Certifications and Declarations

Pin #	Assignment	Description	Pin #	Assignment	Description
74	3.3 V	Primary Power	75	GND	Ground
72	3.3 V	Primary Power	73	GND	Ground
70	3.3 V	Primary Power	71	GND	Ground
68	SUSCLK	Floated	69	PEDET(NC-PCIe)	Floated
58	Reserved for MFG CLOCK	Floated	67	Not Used	
56	Reserved for MFG DATA	Floated	57	GND	Ground
54	PEWAKE#	Floated	55	REFCLKp	PCIe Reference Clock +
52	CLKREQ#		53	REFCLKn	PCIe Reference Clock -
50	PERST#		51	GND	Ground
48	Not Used	Floated	49	PERp0	PCIe Receive- (lane 0)
46	Not Used		47	PERn0	PCIe Receive+ (lane 0)
44	ALERT#	SMBUS_alert	45	GND	Ground
42	SMDAT	SMBUS_data	43	PETp0	PCIe Transmit+ (lane 0)
40	SMCLK	SMBUS_clock	41	PETn0	PCIe Transmit- (lane 0)
38	Not Used		39	GND	Ground
36	Not Used		37	PERp1	PCIe Receive- (lane 1)
34	Not Used		35	PERn1	PCIe Receive+ (lane 1)
32	Not Used		33	GND	Ground
30	Not Used		31	PETp1	PCIe Transmit+ (lane 1)
28	Not Used		29	PETn1	PCIe Transmit- (lane 1)
26	Not Used		27	GND	Ground
24	Not Used		25	PERp2	PCIe Receive- (lane 2)
22	Not Used		23	PERn2	PCIe Receive+ (lane 2)
20	Not Used		21	GND	Ground
18	3.3 V	Primary Power	19	PETp2	PCIe Transmit+ (lane 2)
16	3.3 V	Primary Power	17	PETn2	PCIe Transmit- (lane 2)
14	3.3 V	Primary Power	15	GND	Ground
12	3.3 V	Primary Power	13	PERp3	PCIe Receive- (lane 3)
10	LED1#	Drive Active Signal	11	PERn3 ¹⁾	PCIe Receive+ (lane 3)
8	Not Used		9	GND	Ground
6	Not Used		7	PETp3	PCIe Transmit+ (lane 3)
4	3.3 V	Primary Power	5	PETn3	PCIe Transmit- (lane 3)

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2	3.3 V	Primary Power	3	GND	Ground
			1	GND	Ground

NOTE:

1) LED doesn't blink in Idle state.

LED blinking rate is 50ms(40 to 60ms) in Outstanding IO state(Read, Write).

LED blinking rate is 100ms(80 to 120ms) in following state(Sanitize, SMART Self-Test off-line, SCT WriteSame).

5.0 PCI and NVM EXPRESS REGISTERS

5.1 PCI Express Registers

5.1.1 PCI Register Summary

[Table 22] PCI Register Summary

Start Address	End Address	Name	Type
00h	3Fh	PCI Header	PCI Configuration Header Space
40h	47h	PCI Power Management Capability	PCI Capability
50h	67h	MSI Capability	PCI Capability
70h	A3h	PCI Express Capability	PCI Capability
B0h	BBh	MSI-X Capability	PCI Capability
100h	12Bh	Advanced Error Reporting (AER) Capability	PCI Extended Capability
168h	16Fh	Alternative Routing-ID (ARI) Capability	PCI Extended Capability
178h	18Bh	Secondary PCI Express Capability	PCI Extended Capability
198h	1BBh	Physical Layer 16.0 GT/s Capability	PCI Extended Capability
1BCh	1D3h	Margining Extended Capability Header	PCI Extended Capability
3A0h	3ABh	Data Link Feature Extended Capability	PCI Extended Capability

5.1.2 PCI Header Registers

[Table 23] PCI Header Register Summary

Start Address	End Address	Symbol	Description
00h	03h	ID	Identifiers
04h	05h	CMD	Command Register
06h	07h	STS	Device Status
08h	08h	RID	Revision ID
09h	0Bh	CC	Class Codes
0Ch	0Ch	CLS	Cache Line Size
0Dh	0Dh	MLT	Master Latency Timer
0Eh	0Eh	HTYPE	Header Type
0Fh	0Fh	BIST	Built in Self Test
10h	13h	MLBAR (BAR0)	Memory Register Base Address (lower 32-bit)
14h	17h	MUBAR (BAR1)	Memory Register Base Address (upper 32-bit)
18h	1Bh	IDBAR (BAR2)	Index/Data Pair Register Base Address
1Ch	1Fh	BAR3	Reserved
20h	23h	BAR4	Reserved
24h	27h	BAR5	Reserved
28h	2Bh	CCPTR	CardBus CIS Pointer
2Ch	2Fh	SS	Subsystem Identifiers
30h	33h	EROM	Expansion ROM Base Address
34h	34h	CAP	Capabilities Pointer
35h	3Bh	RO	Reserved
3Ch	3Dh	INTR	Interrupt Information
3Eh	3Eh	MGNT	Minimum Grant
3Fh	3Fh	MLAT	Maximum Latency

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[Table 24] Identifier Register

Bits	Type	Default Value	Description
31:16	RO	A80Ah	Device ID
0:15	RO	144Dh	Vendor ID

[Table 25] Command Register

Bits	Type	Default Value	Description
15:11	RsvdP	0h	Reserved
10	RW	0h	Interrupt Disable
9	RO	0h	Fast Back-to-Back Enable (N/A)
8	RW	0h	SERR# Enable
7	RO	0h	IDSEL Stepping/Wait Cycle Control (N/A)
6	RW	0h	Parity Error Response Enable
5	RO	0h	VGA Palette Snooping Enable (N/A)
4	RO	0h	Memory Write and Invalidate Enable (N/A)
3	RO	0h	Special Cycle Enable (N/A)
2	RW	0h	Bus Master Enable
1	RW	0h	Memory Space Enable
0	RW	0h	I/O Space Enable

[Table 26] Status Register

Bits	Type	Default Value	Description
15	RW1C	0h	Detected Parity Error
14	RW1C	0h	Signaled System Error
13	RW1C	0h	Received Master Abort
12	RW1C	0h	Received Target Abort
11	RO	0h	Reserved
10:9	RO	0h	DEVSEL Timing (N/A)
8	RW1C	0h	Master Data Parity Error Detected
7	RO	0h	Fast Back-to-Back Transaction Capable (N/A)
6	RsvdZ	0h	Reserved
5	RO	0h	66MHz Capable (N/A)
4	RO	1h	Capabilities List
3	RO	0h	Interrupt Status
2:1	RsvdZ	0h	Reserved
0	RO	0h	Reserved

[Table 27] Revision ID Register

Bits	Type	Default Value	Description
7:0	RO	0h	Controller Hardware Revision ID

[Table 28] Class Code Register

Bits	Type	Default Value	Description
23:16	RO	1h	Base Class Code
15:8	RO	8h	Sub Class Code
7:0	RO	2h	Programming Interface

[Table 29] Cache Line Size Register

Bits	Type	Default Value	Description
7:0	RW	0h	Cache Line Size (N/A)

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[Table 30] Master Latency Timer Register

Bits	Type	Default Value	Description
7:0	RO	0h	Master Latency Timer (N/A)

[Table 31] Header Type Register

Bits	Type	Default Value	Description
7	RO	0h	Multi-Function Device
6:0	RO	0h	Header Layout

[Table 32] Built In Self Test Register

Bits	Type	Default Value	Description
7	HwInit	0h	Built In Self Test (N/A)
6	RW/RO	0h	Start BIST (N/A)
5:4	RsvdP	0h	Reserved
3:0	RO	0h	Completion Code (N/A)

[Table 33] Memory Register Base Address Lower 32-bits (BAR0) Register

Bits	Type	Default Value	Description
31:14	RW	0h	Base Address
13:4	RO	0h	Reserved
3	RO	0h	Pre-Fetchable
2:1	RO	2h	Address Type (64-bit)
0	RO	0h	Memory Space Indicator (MEMSI)

[Table 34] Memory Register Base Address Upper 32-bits (BAR1)

Bits	Type	Default Value	Description
31:0	RO	0h	Base Address

[Table 35] Index/Data Pair Register Base Address (BAR2) Register

Bits	Type	Default Value	Description
31:0	RO	0h	N/A

[Table 36] BAR3 Register

Bits	Type	Default Value	Description
31:0	RO	0h	N/A

[Table 37] Vendor Specific BAR4 Register

Bits	Type	Default Value	Description
31:0	RO	0h	N/A

[Table 38] Vendor Specific BAR5 Register

Bits	Type	Default Value	Description
31:0	RO	0h	N/A

[Table 39] Cardbus CIS Pointer Register

Bits	Type	Default Value	Description
31:0	RO	0h	N/A

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[Table 40] Subsystem Identifier Register

Bits	Type	Default Value	Description
31:16	RO	A812h	Subsystem ID
15:0	RO	144Dh	Subsystem Vendor ID

[Table 41] Expansion ROM Register

Bits	Type	Default Value	Description
31:17	RW	0h	Expansion ROM Base Address
16:1	RO	0h	Reserved
0	RW	0h	Expansion ROM Enable/Disable

[Table 42] Capabilities Pointer Register

Bits	Type	Default Value	Description
7:0	RO	40h	Capability Pointer (Points to PCI Power Management Capability Offset)

[Table 43] Interrupt Information Register

Bits	Type	Default Value	Description
15:8	RO	01h	Interrupt Pin
7:0	RW	FFh	Interrupt Line

[Table 44] Minimum Grant Register

Bits	Type	Default Value	Description
7:0	RO	0h	Minimum Grant (N/A)

[Table 45] Maximum Latency Register

Bits	Type	Default Value	Description
7:0	RO	0h	Maximum Latency (N/A)

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5.1.3 PCI Power Management Registers

[Table 46] PCI Power Management Capability Register Summary

Start Address	End Address	Symbol	Description
40h	40h	PCIPM_ID	PCI Power Management Capability ID
41h	41h	NEXTCAP	Next Capability Pointer
42h	43h	PCIPM_CAP	PC Power Management Capabilities
44h	45h	PCIPM_CS	PCI Power Management Control and Status
46h	46h	PCIPM_CSR_BSE	PMCSR_BSE Bridge Extensions
47h	47h	PCIEPM_DATA	Data

[Table 47] PCI Power Management Capability ID Register

Bits	Type	Default Value	Description
15:8	RO	50h	Next Capability
7:0	RO	1h	Capability ID

[Table 48] PCI Power Management Capability Register

Bits	Type	Default Value	Description
15:11	RO	0h	PME Support
10	RO	0h	D2 Support
9	RO	0h	D1 Support
8:6	RO	0h	AUX Current
5	RO	0h	Device Specific Initialization
4	RO	0h	Immediate Readiness on Return to D0
3	RO	0h	PME Clock (N/A)
2:0	RO	3h	Version (Support for PCIe Power Management Interface Spec revision 1.2)

[Table 49] PCI Power Management Control and Status Register

Bits	Type	Default Value	Description
31:24	RO	0h	Data register (N/A)
23	RO	0h	Bus Power/Clock Enable (N/A)
22	RO	0h	B2 , B3 support (N/A)
21:16	RsvdP	0h	Reserved
15	RW1CS	0h	PME_Status
14:13	RO	0h	Data Scale (N/A)
12:9	RO	0h	Data Select (N/A)
8	RW1CS	0h	PME enable
7:4	RsvdP	0h	Reserved
3	RO	1h	No Soft Reset
2	RsvdP	0h	Reserved
1:0	RW	0h	Power State

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5.1.4 Message Signaled Interrupt Registers

[Table 50] Message Signaled Interrupt Capability Register Summary

Start Address	End Address	Symbol	Description
50h	51h	MSI_ID	Message Signaled Interrupt Capability ID
52h	53h	MSI_MC	Message Signaled Interrupt Message Control
54h	57h	MSI_MA	Message Signaled Interrupt Message Address
58h	5Bh	MSI_MUA	Message Signaled Interrupt Upper Address
5Ch	5Dh	MSI_MDATA	Message Signaled Interrupt Message Data
60h	63h	MSI_MMASK	Message Signaled Interrupt Mask Bits
64h	67h	MSI_MPEND	Message Signaled Interrupt Pending Bits

[Table 51] Message Signaled Interrupt Capability ID Register

Bits	Type	Default Value	Description
15:8	RO	70h	Next Capability
7:0	RO	05h	Capability ID

[Table 52] Message Signaled Interrupt Control Register

Bits	Type	Default Value	Description
15:11	RsvdP	0h	Reserved
10	RW	0h	Extended Message Data Enable
9	RO	0h	Extended Message Data Capable
8	RO	0h	Per Vector Masking Capable
7	RO	1h	64-bit Address Capable
6:4	RW	0h	Multiple Message Enable
3:1	RO	5h	Multiple Message Capable
0	RW	0h	MSI Enable

[Table 53] Message Signaled Interrupt Lower Address Register

Bits	Type	Default Value	Description
31:2	RW	0h	Message Address
1:0	RsvdP	0h	Reserved

[Table 54] Message Signaled Interrupt Upper Address Register

Bits	Type	Default Value	Description
31:0	RW	0h	Message Upper Address

[Table 55] Message Signaled Interrupt Message Data Register

Bits	Type	Default Value	Description
31:16	RW	0h	Extended Message Data
0:15	RW	0h	Data

[Table 56] Message Signaled Interrupt Mask Bits Register

Bits	Type	Default Value	Description
31:0	RW	0h	Mask Bits

[Table 57] Message Signaled Interrupt Pending Bits Register

Bits	Type	Default Value	Description
31:0	RO	0h	Pending Bits

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5.1.5 PCI Express Capability Registers

[Table 58] PCI Express Capability Register Summary

Start Address	End Address	Symbol	Description
70h	71h	PCIE_ID	PCI Express Capability ID
72h	73h	PCIE_CAP	PCI Express Capabilities
74h	77h	PCIE_DCAP	PCI Express Device Capabilities
78h	79h	PCIE_DC	PCI Express Device Control
7Ah	7Bh	PCIE_DS	PCI Express Device Status
7Ch	7Fh	PCIE_LCAP	PCI Express Link Capabilities
80h	81h	PCIE_LC	PCI Express Link Control
82h	83h	PCIE_LS	PCI Express Link Status
94h	97h	PCIE_DCAP2	PCI Express Device Capabilities 2
98h	99h	PCIE_DC2	PCI Express Device Control 2
9Ah	9Bh	PCIE_DS2	PCI Express Device Status 2
9Ch	9Fh	PCIE_LCAP2	PCI Express Link Capabilities 2
A0h	A1h	PCIE_LC2	PCI Express Link Control 2
A2h	A3h	PCIE_LS2	PCI Express Link Status 2

[Table 59] PCI Express Capability ID Register

Bits	Type	Default Value	Description
15:8	RO	B0h	Next Pointer (MSI-X Capability)
7:0	RO	10h	Capability ID

[Table 60] PCI Express Capabilities Register

Bits	Type	Default Value	Description
15	RsvdP	0h	Reserved
14	RO	0h	Reserved
13:9	RO	0h	Interrupt Message Number
8	HwInit	0h	Slot Implementation (N/A)
7:4	RO	0h	Device/Port Type
3:0	RO	2h	Capability Version

[Table 61] PCI Express Device Capabilities Register

Bits	Type	Default Value	Description
31:29	RsvdP	0h	Reserved
28	RO	1h	Function Level Reset Capability
27:26	RO	0h	Captured Slot Power Limit Scale
25:18	RO	0h	Captured Slot Power Limit Value
17:16	RsvdP	0h	Reserved
15	RO	1h	Role-based Error Reporting
14:12	RO	0h	Reserved
11:9	RO	7h	Endpoint L1 Acceptable Latency
8:6	RO	7h	Endpoint L0 Acceptable Latency
5	RO	1h	Extended Tag Field Supported
4:3	RO	0h	Phantom Functions Supported
2:0	RO	1h	Max Payload Size Supported (256 byte payload)

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[Table 62] PCI Express Device Control Register

Bits	Type	Default Value	Description
15	RO	0h	Initiate Function Level Reset
14:12	RW	2h	Max Read Request Size
11	RW	1h	Enable No Snoop
10	RWS	0h	Aux Power PM Enable (N/A)
9	RW	0h	Phantom Functions Enable (N/A)
8	RW	1h	Extended Tag Enable
7:5	RW	0h	Max Payload Size
4	RW	1h	Enable Relaxed Ordering
3	RW	0h	Unsupported Request Reporting Enable
2	RW	0h	Fatal Error Reporting Enable
1	RW	0h	Non-Fatal Error Reporting Enable
0	RW	0h	Correctable Error Reporting Enable

[Table 63] PCI Express Device Status Register

Bits	Type	Default Value	Description
15:7	RsvdZ	0h	Reserved
6	RO	0h	Emergency Power Reduction Detected (N/A)
5	RO	0h	Transactions Pending
4	RW	0h	Aux Power Detected
3	RW1C	0h	Unsupported Request Detected
2	RW1C	0h	Fatal Error Detected
1	RW1C	0h	Non-Fatal Error Detected
0	RW1C	0h	Correctable Error Detected

[Table 64] PCI Express Link Capabilities Register

Bits	Type	Default Value	Description
31:24	HwInit	0h	Port Number(Port 0)
23	RsvdP	0h	Reserved
22	HwInit	1h	ASPM Optionality Compliance
21	RO	0h	Link Bandwidth Notification Capability
20	RO	0h	Data Link Layer Link Active Reporting Capable
19	RO	0h	Surprise Down Error Reporting Capable
18	RO	0h	Clock Power Management
17:15	RO	6h	L1 Exit Latency
14:12	RO	7h	L0s Exit Latency
11:10	RO	0h	Active State Power Management Support
9:4	RO	4h	Maximum Link Width - (x4 link)
3:0	RO	4h	Supported Link Speeds - PCIe Gen3(3h), Gen4(4h)

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[Table 65] PCI Express Link Control Register

Bits	Type	Default Value	Description
15:14	RW/RsvdP	0h	DRS Signaling Control (N/A)
13:12	RsvdP	0h	Reserved
11	RsvdP	0h	Link Autonomous Bandwidth Interrupt Enable (N/A)
10	RsvdP	0h	Link Bandwidth Management Interrupt Enable (N/A)
9	RsvdP	0h	Hardware Autonomous Width Disable
8	RW	0h	Enable Clock Power Management
7	RW	0h	Extended Sync
6	RW	0h	Common Clock Configuration
5	RsvdP	0h	Retrain Link (N/A)
4	RsvdP	0h	Link Disable (N/A)
3	RW	0h	Read Completion Boundary
2	RsvdP	0h	Reserved
1:0	RW	0h	Active State Power Management Control

[Table 66] PCI Express Link Status Register

Bits	Type	Default Value	Description
15	RO	0h	Link Autonomous Bandwidth Status (N/A)
14	RO	0h	Link Bandwidth Management Status (N/A)
13	RO	0h	Data Link Layer Link Active
12	HwInit	1h	Slot Clock Configuration
11	RO	0h	Link Training (N/A)
10	RO	0h	Reserved
9:4	RO	1h	Negotiated Link Width
3:0	RO	1h	Current Link Speed

[Table 67] PCI Express Device Capabilities 2 Register

Bits	Type	Default Value	Description
31	HwInit	0h	FRS Supported
30:27	RsvdP	0h	Reserved
26	RO	0h	Emergency Power Reduction Initialization Required (N/A)
25:24	RO	0h	Emergency Power Reduction Supported (N/A)
23:22	HwInit	0h	Max End-End TLP Prefixes
21	HwInit	0h	End-End TLP Prefix Supported
20	RO	0h	Extended Format Field Supported
19:18	HwInit	0h	OBFF Supported
17	HwInit	0h	10-Bit Tag Requester Supported
16	HwInit	0h	10-Bit Tag Completer Supported
15:14	HwInit	0h	LN System CLS (N/A)
13:12	RO	0h	TPH Completer Supported
11	RO	1h	Latency Tolerance Reporting Supported
10	HwInit	0h	No RO-enabled PR-PR Passing (N/A)
9	RO	0h	128-bit CAS Completer Supported
8	RO	0h	64-bit Atomic Op Completer Supported
7	RO	0h	32-bit Atomic Op Completer Supported
6	RO	0h	Atomic Op Routing Supported (N/A)
5	RO	0h	ARI Forwarding Supported (N/A)
4	RO	1h	Completion Timeout Disable Supported
3:0	HwInit	Fh	Completion Timeout Ranges Supported

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PCI Express Device Control 2 Register

Bits	Type	Default Value	Description
15	RsvdP	0h	End-to-end TLP Prefix Blocking
14:13	RW/RsvdP	0h	OBFF Enable
12	RW	0h	10-Bit Tag Requester Enable
11	RO	0h	Emergency Power Reduction Request (N/A)
10	RW/RsvdP	1h	Latency Tolerance Reporting Mechanism Enable
9	RW	0h	IDO Completion Enable
8	RW	0h	IDO Request Enable
7	RW	0h	AtomicOp Egress Blocking (N/A)
6	RW	0h	AtomicOp Requester Enable
5	RW	0h	ARI Forwarding Enable (N/A)
4	RW	0h	Completion Timeout Disable
3:0	RW	0h	Completion Timeout Value

[Table 68] PCI Express Device Status 2 Register

Bits	Type	Default Value	Description
15:0	RsvdZ	0h	Reserved

[Table 69] PCI Express Link Capabilities 2 Register

Bits	Type	Default Value	Description
31	RO	0h	DRS supported
30:25	RsvdP	0h	Reserved
24	HWinit	0h	Two Retimers Presence Detect Supported
23	HWinit	0h	Retimer Presence Detect Supported
22:16	RO	0h	Lower SKP OS Reception Supported Speed Vector
15:9	RO	0h	Lower SKP OS Generation Supported Speed Vector
8	RO	0h	Cross-Link Supported
7:1	RO	Fh	Supported Speeds Vector - PCIe Gen3(7h), Gen4(Fh)
0	RsvdP	0	Reserved

[Table 70] PCI Express Link Control 2 Register

Bits	Type	Default Value	Description
15:12	RWS/RsvdP	0h	Compliance De-emphasis
11	RWS/RsvdP	0h	Compliance SOS
10	RWS/RsvdP	0h	Enter Modified Compliance
9:7	RWS/RsvdP	0h	Transmit Margin
6	HwInit	0h	Selectable De-Emphasis (N/A)
5	RWS/RsvdP	0h	Hardware Autonomous Speed Disable
4	RWS/RsvdP	0h	Enter Compliance
3:0	RWS/RsvdP	4h	Target Link Speed 1h: 2.5 GT/s (Gen 1) 2h: 5.0 GT/s (Gen 2) 3h: 8 GT/s (Gen 3) 4h: 16 GT/s (Gen 4)

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[Table 71] PCI Express Link Status 2 Register

Bits	Type	Default Value	Description
15	RO	0h	DRS Message Received (N/A)
14:12	RO	0h	Downstream Componenet Present (N/A)
11:10	RsvdZ	0h	Reserved
9:8	RO	1h	Crosslink Resolution
7	ROS/RsvdZ	0h	Two Retimers Presence Detected
6	ROS/RsvdZ	0h	Retimer Presence Detected
5	RW1CS	0h	Link Equalization Request
4	ROS	0h	Equalization Phase 3 Successful
3	ROS	0h	Equalization Phase 2 Successful
2	ROS	0h	Equalization Phase 1 Successful
1	ROS	0h	Equalization Complete
0	RO	1h	Current De-Emphasis

5.1.6 MSI-X Registers

[Table 72] MSI-X Capability Register Summary

Start Address	End Address	Symbol	Description
B0h	B1h	MSIX_ID	MSI-X Capability ID
B2h	B3h	MSIX_CAP	MSI-X Message Control
B4h	B7h	MSIX_TBL	MSI-X Table Offset and Table BIR
B8h	BBh	MSIX_PBA	MSI-X PBA Offset and PBA BIR

[Table 73] MSI-X Identifier Register

Bits	Type	Default Value	Description
15:8	RO	00h	Next Capability
7:0	RO	11h	Capability ID

[Table 74] MSI-X Control Register

Bits	Type	Default Value	Description
15	RW	0h	MSI-X Enable
14	RW	0h	Function Mask
13:11	RsvdP	0h	Reserved
10:0	RO	81h	Table Size

[Table 75] MSI-X Table Offset Register

Bits	Type	Default Value	Description
31:3	RO	600h	Table Offset
2:0	RO	0h	Table BIR

[Table 76] MSI-X Pending Bit Array Offset Register

Bits	Type	Default Value	Description
31:3	RO	400h	Pending Bit Array Offset
2:0	RO	0h	Pending Bit Array BIR

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5.1.7 Advanced Error Reporting Registers

[Table 77] Advanced Error Reporting Capability Register Summary

Start Address	End Address	Symbol	Description
100h	103h	AER_ID	AER Capability ID
104h	107h	AER_UCES	AER Uncorrectable Error Status
108h	10Bh	AER_UCEM	AER Uncorrectable Error Mask
10Ch	10Fh	AER_UCESEV	AER Uncorrectable Error Severity
110h	113h	AER_CES	AER Correctable Error Status
114h	117h	AER_CEM	AER Correctable Error Mask
118h	11Bh	AER_CC	AER Advanced Error Capabilities and Control
11Ch	12Bh	AER_HL	AER Header Log

[Table 78] AER Capability ID Register

Bits	Type	Default Value	Description
31:20	RO	168h	Next Pointer (Points to Alternative Routing-ID Capability Header Offset)
19:16	RO	2h	Capability Version
15:0	RO	1h	Capability ID

[Table 79] AER Uncorrectable Error Status Register

Bits	Type	Default Value	Description
31:27	RsvdZ	0h	Reserved
26	RW1CS	0h	Poisoned TLP Egress Blocked Status
25	RW1CS	0h	TLP Prefix Blocked Error Status
24	RW1CS	0h	Atomic Op Egress Blocked Status
23	RW1CS	0h	MC Blocked TLP Status
22	RW1CS	0h	Uncorrectable Internal Error Status
21	RW1CS	0h	ACS Violation Status
20	RW1CS	0h	Unsupported Request Error Status
19	RW1CS	0h	ECRC Error Status
18	RW1CS	0h	Malformed TLP Status
17	RW1CS	0h	Receiver Overflow Status
16	RW1CS	0h	Unexpected Completion Status
15	RW1CS	0h	Completer Abort Status
14	RW1CS	0h	Completion Timeout Status
13	RW1CS	0h	Flow Control Protocol Error Status
12	RW1CS	0h	Poisoned TLP Status
11:6	RsvdZ	0h	Reserved
5	RW1CS	0h	Surprise Down Error Status (N/A)
4	RW1CS	0h	Data Link Protocol Error Status
3:1	RsvdZ	0h	Reserved
0	Undefined	0h	Undefined

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[Table 80] AER Uncorrectable Error Mask Register

Bits	Type	Default Value	Description
31:27	RsvdZ	0h	Reserved
26	RWS	0h	Poisoned TLP Egress Blocked Mask
25	RWS	0h	TLP Prefix Blocked Error Mask
24	RWS	0h	Atomic Op Egress Blocked Mask
23	RWS	0h	MC Blocked TLP Mask
22	RWS	1h	Uncorrectable Internal Error Mask
21	RWS	0h	ACS Violation Mask
20	RWS	0h	Unsupported Request Error Mask
19	RWS	0h	ECRC Error Mask
18	RWS	0h	Malformed TLP Mask
17	RWS	0h	Receiver Overflow Mask
16	RWS	0h	Unexpected Completion Mask
15	RWS	0h	Completer Abort Mask
14	RWS	0h	Completion Timeout Mask
13	RWS	0h	Flow Control Protocol Error Mask
12	RWS	0h	Poisoned TLP Mask
11:6	RsvdZ	0h	Reserved
5	RWS	0h	Surprise Down Error Mask (N/A)
4	RWS	0h	Data Link Protocol Error Mask
3:1	RsvdZ	0h	Reserved
0	Undefined	0h	Undefined

[Table 81] AER Uncorrectable Error Severity Register

Bits	Type	Default Value	Description
31:27	RsvdP	0h	Reserved
26	RWS	0h	Poisoned TLP Egress Blocked Severity
25	RWS	0h	TLP Prefix Blocked Error Severity
24	RWS	0h	Atomic Op Egress Blocked Severity
23	RWS	0h	MC Blocked TLP Severity
22	RWS	1h	Uncorrectable Internal Error Severity
21	RWS	0h	ACS Violation Severity
20	RWS	0h	Unsupported Request Error Severity
19	RWS	0h	ECRC Error Severity
18	RWS	1h	Malformed TLP Severity
17	RWS	1h	Receiver Overflow Severity
16	RWS	0h	Unexpected Completion Severity
15	RWS	0h	Completer Abort Severity
14	RWS	0h	Completion Timeout Severity
13	RWS	1h	Flow Control Protocol Error Severity
12	RWS	0h	Poisoned TLP Severity
11:6	RsvdP	0h	Reserved
5	RWS	1h	Surprise Down Error Severity (N/A)
4	RWS	1h	Data Link Protocol Error Severity
3:1	RsvdP	0h	Reserved
0	Undefined	0h	Undefined

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[Table 82] AER Correctable Error Status Register

Bits	Type	Default Value	Description
31:16	RsvdZ	0h	Reserved
15	RW1CS	0h	Header Log Overflow Status
14	RW1CS	0h	Corrected Internal Error Status
13	RW1CS	0h	Advisory Non-Fatal Error Status
12	RW1CS	0h	Replay Timer Timeout Status
11:9	RsvdZ	0h	Reserved
8	RW1CS	0h	Replay Number Rollover Status
7	RW1CS	0h	Bad DLLP Status
6	RW1CS	0h	Bad TLP Status
5:1	RsvdZ	0h	Reserved
0	RW1CS	0h	Received Error Status

[Table 83] AER Correctable Error Mask Register

Bits	Type	Default Value	Description
31:16	RsvdP	0h	Reserved
15	RWS	1h	Header Log Overflow Status
14	RWS	1h	Corrected Internal Error Mask
13	RWS	1h	Advisory Non-Fatal Error Mask
12	RWS	0h	Replay Timer Timeout Mask
11:9	RsvdP	0h	Reserved
8	RWS	0h	Replay Number Rollover Mask
7	RWS	0h	Bad DLLP Mask
6	RWS	0h	Bad TLP Mask
5:1	RsvdP	0h	Reserved
0	RWS	0h	Received Error Mask

[Table 84] AER Capabilities and Control Register

Bits	Type	Default Value	Description
31:13	RsvdP	0h	Reserved
12	RO	0h	Completion Timeout Prefix/Header Log Capable
11	ROS	0h	TLP Prefix Log Present
10	RWS	0h	Multiple Header Recording Enable
9	RO	1h	Multiple Header Recording Capable
8	RWS	0h	ECRC Check Enable
7	RO	1h	ECRC Check Capable
6	RWS	0h	ECRC Generation Enable
5	RO	1h	ECRC Generation Capable
4:0	ROS	0h	First Error Pointer

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[Table 85] AER Header Log Register

Bits	Type	Default Value	Description
127:120	ROS	0h	Header Byte 0
119:112	ROS	0h	Header Byte 1
111:104	ROS	0h	Header Byte 2
103:96	ROS	0h	Header Byte 3
95:88	ROS	0h	Header Byte 4
87:80	ROS	0h	Header Byte 5
79:72	ROS	0h	Header Byte 6
71:64	ROS	0h	Header Byte 7
63:56	ROS	0h	Header Byte 8
55:48	ROS	0h	Header Byte 9
47:40	ROS	0h	Header Byte 10
39:32	ROS	0h	Header Byte 11
31:24	ROS	0h	Header Byte 12
23:16	ROS	0h	Header Byte 13
15:8	ROS	0h	Header Byte 14
7:0	ROS	0h	Header Byte 15

5.1.8 Alternative Routing-ID (ARI) Capability Registers

[Table 86] Alternative Routing-ID (ARI) Capability Summary

Start Address	End Address	Symbol	Description
168h	16Bh	ARI_ID	Alternative Routing-ID (ARI) Capability Header
16Ch	16Dh	ARI_CAP	ARI Capability Register
16Eh	16Fh	ARI_CON	ARI Control Register

[Table 87] Alternative Routing-ID (ARI) Capability Header

Bits	Type	Default Value	Description
31:20	RO	178h	Next Capability Offset (Points to Secondary PCI Express Extended capability Header Offset)
19:16	RO	1h	Capability Version
15:0	RO	Eh	PCI Express Extended Capability ID

[Table 88] Alternative Routing-ID (ARI) Capability Register

Bits	Type	Default Value	Description
15:8	RO	0h	Next Function Number
7:2	RsvdP	0h	Reserved
1	RO	0h	ACS Function Groups Capability (A)
0	RO	0h	MFVC Function Groups Capability (M)

[Table 89] Alternative Routing-ID (ARI) Control Register

Bits	Type	Default Value	Description
15:7	RsvdP	0h	Reserved
6:4	RO	0h	Function Group
3:2	RsvdP	0h	Reserved
1	RO	0h	ACS Function Groups Enable (A)
0	RO	0h	MFVC Function Groups Enable (M)

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5.1.9 Secondary PCI Express Capability Registers

[Table 90] Secondary PCI Express Capability Register Summary

Start Address	End Address	Symbol	Description
178h	17Bh	SPE_ID	Secondary PCI Express Capability
17Ch	17Fh	PCIE_LC3	PCI Express Link Control 3
180h	183h	PCIE_LE	PCI Express Lane Error Status
184h	185h	PCIE_L0EC	PCI Express Lane 0 Equalization Control
186h	187h	PCIE_L1EC	PCI Express Lane 1 Equalization Control
188h	189h	PCIE_L2EC	PCI Express Lane 2 Equalization Control
18Ah	18Bh	PCIE_L3EC	PCI Express Lane 3 Equalization Control

[Table 91] Secondary PCI Express Capability ID Register

Bits	Type	Default Value	Description
31:20	RO	198h	Next Pointer – Gen4(198h), Gen3(0h)
19:16	RO	1h	Capability Version
15:0	RO	19h	Capability ID (Secondary PCI Express Extended capability)

[Table 92] PCI Express Link Control 3 Register

Bits	Type	Default Value	Description
31:16	Rsvdp	0h	Reserved
15:9	RW	0h	Enable Lower SKP OS Generation Vector
8:2	RsvdP	0h	Reserved
1	RW	0h	Link Equalization Request Interrupt Enable
0	RW	0h	Perform Equalization (N/A)

[Table 93] PCI Express Lane Error Status Register

Bits	Type	Default Value	Description
31:4	Rsvdp	0h	Reserved
3:0	RW1CS	0h	Lane Error Status Bits

[Table 94] PCI Express Lane 0 Equalization Register

Bits	Type	Default Value	Description
15	RsvdP	0h	Reserved
14:12	HwInit/RO	7h	Upstream Port 8.0T/s Receiver Preset Hint
11:8	HwInit/RO	4h	Upstream Port 8.0T/s Transmitter Preset
7	RsvdP	0h	Reserved
6:4	HwInit/RsvdP	0h	Downstream Port 8.0T/s Receiver Preset Hint (N/A)
3:0	HwInit/RsvdP	0h	Downstream Port 8.0T/s Transmitter Preset (N/A)

[Table 95] PCI Express Lane 1 Equalization Register

Bits	Type	Default Value	Description
15	RsvdP	0h	Reserved
14:12	HwInit/RO	7h	Upstream Port 8.0T/s Receiver Preset Hint
11:8	HwInit/RO	4h	Upstream Port 8.0T/s Transmitter Preset
7	RsvdP	0h	Reserved
6:4	HwInit/RsvdP	0h	Downstream Port 8.0T/s Receiver Preset Hint (N/A)
3:0	HwInit/RsvdP	0h	Downstream Port 8.0T/s Transmitter Preset (N/A)

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[Table 96] PCI Express Lane 2 Equalization Register

Bits	Type	Default Value	Description
15	RsvdP	0h	Reserved
14:12	HwInit/RO	7h	Upstream Port 8.0T/s Receiver Preset Hint
11:8	HwInit/RO	4h	Upstream Port 8.0T/s Transmitter Preset
7	RsvdP	0h	Reserved
6:4	HwInit/RsvdP	0h	Downstream Port 8.0T/s Receiver Preset Hint (N/A)
3:0	HwInit/RsvdP	0h	Downstream Port 8.0T/s Transmitter Preset (N/A)

[Table 97] PCI Express Lane 3 Equalization Register

Bits	Type	Default Value	Description
15	RsvdP	0h	Reserved
14:12	HwInit/RO	7h	Upstream Port 8.0T/s Receiver Preset Hint
11:8	HwInit/RO	4h	Upstream Port 8.0T/s Transmitter Preset
7	RsvdP	0h	Reserved
6:4	HwInit/RsvdP	0h	Downstream Port 8.0T/s Receiver Preset Hint (N/A)
3:0	HwInit/RsvdP	0h	Downstream Port 8.0T/s Transmitter Preset (N/A)

5.1.10 Physical Layer 16.0 GT/s Capability

[Table 98] Physical Layer 16.0 GT/s Capability Summary

Start Address	End Address	Symbol	Description
198h	19Bh		Physical Layer 16.0 GT/s Extended Capability Header
19Ch	19Fh		16.0 GT/s Capabilities Register
1A0h	1A3h		16.0 GT/s Control Register
1A4h	1A7h		16.0 GT/s Status Register
1A8h	1ABh		16.0 GT/s Local Data Parity Mismatch Status Register
1ACh	1AFh		16.0 GT/s First Retimer Data Parity Mismatch Status Register
1B0h	1B3h		16.0 GT/s Second Retimer Data Parity Mismatch Status Register
1B4h	1B7h		Reserved
1B8h	1BBh		16.0 GT/s Control Register for Lane 0-3

[Table 99] Physical Layer 16.0 GT/s Extended Capability Header

Bits	Type	Default Value	Description
31:20	RO	1BCh	Next Capability Offset
19:16	RO	1h	Capability Version
15:0	RO	26h	Capability ID (Secondary PCI Express Extended capability)

[Table 100] 16.0 GT/s Capabilities Register

Bits	Type	Default Value	Description
31:0	RsvdP	0	Reserved

[Table 101] 16.0 GT/s Control Register

Bits	Type	Default Value	Description
31:0	RsvdP	0	Reserved

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[Table 102] 16.0 GT/s Status Register

Bits	Type	Default Value	Description
31:5	RsvdZ	0	Reserved
4	RW1CS	0	Link Equalization Request 16.0 GT/s
3	ROS	0	Equalization 16.0 GT/s Phase 3 Successful
2	ROS	0	Equalization 16.0 GT/s Phase 2 Successful
1	ROS	0	Equalization 16.0 GT/s Phase 1 Successful
0	ROS	0	Equalization 16.0 GT/s Complete

[Table 103] 16.0 GT/s Local Data Parity Mismatch Status Register

Bits	Type	Default Value	Description
31:4	RsvdP	0	Reserved
3:0	RW1CS	0	Local Data Parity Mismatch Status

[Table 104] 16.0 GT/s First Retimer Data Parity Mismatch Status Register

Bits	Type	Default Value	Description
31:4	RsvdP	0	Reserved
3:0	RW1CS	0	First Retimer Data Parity Mismatch Status

[Table 105] 16.0 GT/s Second Retimer Data Parity Mismatch Status Register

Bits	Type	Default Value	Description
31:4	RsvdP	0	Reserved
3:0	RW1CS	0	Second Retimer Data Parity Mismatch Status

[Table 106] Reserved

Bits	Type	Default Value	Description
31:0	RsvdP	0	Reserved

[Table 107] 16.0 GT/s Control Register for Lane 0-3

Bits	Type	Default Value	Description
31:28	HwInit/RO	4h	Upstream Port 16.0 GT/s Transmitter Preset Lane 3
27:24	HwInit/RsvdP	0h	Downstream Port 16.0 GT/s Transmitter Preset Lane 3 (N/A)
23:20	HwInit/RO	4h	Upstream Port 16.0 GT/s Transmitter Preset Lane 2
19:16	HwInit/RsvdP	0h	Downstream Port 16.0 GT/s Transmitter Preset Lane 2 (N/A)
15:12	HwInit/RO	4h	Upstream Port 16.0 GT/s Transmitter Preset Lane 1
11:8	HwInit/RsvdP	0h	Downstream Port 16.0 GT/s Transmitter Preset Lane 1 (N/A)
7:4	HwInit/RO	4h	Upstream Port 16.0 GT/s Transmitter Preset Lane 0
3:0	HwInit/RsvdP	0h	Downstream Port 16.0 GT/s Transmitter Preset Lane 0 (N/A)

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5.1.11 Margining Extended Capability Header

[Table 108] Margining Extended Capability Header Summary

Start Address	End Address	Symbol	Description
1BCh	1BFh		Margining Extended Capability Header
1C0h	1C1h		Margining Port Capabilities Register
1C2h	1C3h		Margining Port Status Register
1C4h	1C5h		Margining Lane Control Register (Lane 0)
1C6h	1C7h		Margining Lane Status Register (Lane 0)
1C8h	1C9h		Margining Lane Control Register (Lane 1)
1CAh	1CBh		Margining Lane Status Register (Lane 1)
1CCh	1CDh		Margining Lane Control Register (Lane 2)
1CEh	1CFh		Margining Lane Status Register (Lane 2)
1D0h	1D1h		Margining Lane Control Register (Lane 3)
1D2h	1D3h		Margining Lane Status Register (Lane 3)

[Table 109] Physical Layer 16.0 GT/s Margining Capability

Bits	Type	Default Value	Description
31:20	RO	3A0h	Next Capability Offset
19:16	RO	1h	Capability Version
15:0	RO	27h	PCI Express Extended Capability ID

[Table 110] Margining Port Capabilities Register

Bits	Type	Default Value	Description
15:1	RsvdP	0	Reserved
0	HWInit	0	Margining uses Driver Software

[Table 111] Margining Port Status Register

Bits	Type	Default Value	Description
15:2	RsvdP	0	Reserved
1	RO	0	Margining Software Ready
0	RO	0	Margining Ready

[Table 112] Margining Lane Control Register Lane 0

Bits	Type	Default Value	Description
15:8	RW	9Ch	Margin Payload
7	RsvdP	0	Reserved
6	RW	0	Usage Model
5:3	RW	7h	Margin Type
2:0	RW	0	Receiver Number

[Table 113] Margining Lane Status Register Lane 0

Bits	Type	Default Value	Description
15:8	RW	0	MarginPayload Status
7	RsvdP	0	Reserved
6	RW	0	Usage Model Status
5:3	RW	0	Margin Type Status
2:0	RW	0	Receiver Number Status

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[Table 114] Margining Lane Control Register Lane 1

Bits	Type	Default Value	Description
15:8	RW	9Ch	Margin Payload
7	RsvdP	0	Reserved
6	RW	0	Usage Model
5:3	RW	7h	Margin Type
2:0	RW	0	Receiver Number

[Table 115] Margining Lane Status Register Lane 1

Bits	Type	Default Value	Description
15:8	RW	0	MarginPayload Status
7	RsvdP	0	Reserved
6	RW	0	Usage Model Status
5:3	RW	0	Margin Type Status
2:0	RW	0	Receiver Number Status

[Table 116] Margining Lane Control Register Lane 2

Bits	Type	Default Value	Description
15:8	RW	9Ch	Margin Payload
7	RsvdP	0	Reserved
6	RW	0	Usage Model
5:3	RW	7h	Margin Type
2:0	RW	0	Receiver Number

[Table 117] Margining Lane Status Register Lane 2

Bits	Type	Default Value	Description
15:8	RW	0	MarginPayload Status
7	RsvdP	0	Reserved
6	RW	0	Usage Model Status
5:3	RW	0	Margin Type Status
2:0	RW	0	Receiver Number Status

[Table 118] Margining Lane Control Register Lane 3

Bits	Type	Default Value	Description
15:8	RW	9Ch	Margin Payload
7	RsvdP	0	Reserved
6	RW	0	Usage Model
5:3	RW	7h	Margin Type
2:0	RW	0	Receiver Number

[Table 119] Margining Lane Status Register Lane 3

Bits	Type	Default Value	Description
15:8	RW	0	MarginPayload Status
7	RsvdP	0	Reserved
6	RW	0	Usage Model Status
5:3	RW	0	Margin Type Status
2:0	RW	0	Receiver Number Status

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5.1.12 Data Link Feature Extended Capability

[Table 120] Data Link Feature Extended Capability

Start Address	End Address	Symbol	Description
3A0h	3A3h		Data Link Feature Extended Capability Header
3A4h	3A7h		Data Link Feature Capabilities Register
3A8h	3ABh		Data Link Feature Status Register

[Table 121] Data Link Feature Extended Capability Header

Bits	Type	Default Value	Description
31:20	RO	0h	Next Capability Offset
19:16	RO	1h	Capability Version
15:0	RO	25h	PCI Express Extended Capability ID

[Table 122] Data Link Feature Capabilities Register

Bits	Type	Default Value	Description
31	HwInit	1h	Data Link Feature Exchange Enable
30:23	RsvdP	0h	Reserved
22:1	RsvdP	0h	Reserved
0	HwInit	1h	Local Scaled Flow Control Supported

[Table 123] Data Link Feature Status Register

Bits	Type	Default Value	Description
31	RO	0h	Remote Data Link Feature Supported Valid
30:23	RsvdP	0h	Reserved
22:1	RO	0h	Undefined
0	RO	0h	Remote Scaled Flow Control Supported

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5.2 NVM Express Registers

5.2.1 Register Summary

[Table 124] Register Summary

Start Address	End Address	Name	Type
00h	07h	CAP	Controller Capabilities
08h	0Bh	VS	Version
0Ch	0Fh	INTMS	Interrupt Mask Set
10h	13h	INTMC	Interrupt Mask Clear
14h	17h	CC	Controller Configuration
18h	1Bh	Reserved	Reserved
1Ch	1Fh	CSTS	Controller Status
20h	23h	NSSR	NVM Subsystem Reset
24h	27h	AQA	Admin Queue Attributes
28h	2Fh	ASQ	Admin Submission Queue Base Address
30h	37h	ACQ	Admin Completion Queue Base Address
38h	EFFh	Reserved	Reserved
F00h	FFFh	Reserved	Command Set Specific
1000h	1003h	SQ0TDBL	Submission Queue 0 Tail Doorbell (Admin)
1000h + (1 * (4 << CAP.DSTRD))	1003h + (1 * (4 << CAP.DSTRD))	CQ0HDBL	Completion Queue 0 Head Doorbell (Admin)
...			
1000h + (2y * (4 << CAP.DSTRD))	1003h + (2y * (4 << CAP.DSTRD))	SQyTDVL	Submission Queue y Tail Doorbell
1000h + ((2y + 1) * (4 << CAP.DSTRD))	1003h + ((2y + 1) * (4 << CAP.DSTRD))	CQyHDBL	Completion Queue y Head Doorbell

5.2.2 Controller Registers

[Table 125] Controller Capabilities

Bits	Type	Name	Default Value	Description
63:56	RO	-	0h	Reserved
55:52	RO	MPSMAX	0h	Memory Page Size Maximum (Maximum is 4KB)
51:48	RO	MPSMIN	0h	Memory Page Size Minimum (Minimum is 4KB)
47:45	RO	-	0h	Reserved
44:37	RO	CSS	1h	Command Sets Supported 1h: NVM command set
36	RO	NSSRS	1h	NVM Subsystem Reset Supported
35:32	RO	DSTRD	0h	Doorbell Stride 0: Stride of 4 bytes
31:24	RO	TO	28h (960/1920GB) 32h (3840GB)	Timeout(unit:500ms) 28h: 20 seconds, 32h: 25 seconds
23:19	RO	-	0h	Reserved
18:17	RO	AMS	1h	Arbitration Mechanism Supported (Weighted Round Robin with Urgent supported)
16	RO	CQR	1h	Contiguous Queues Required
15:0	RO	MQES	3FFFh	Maximum Queue Entries Supported (16384 entries supported)

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[Table 126] Version

Bits	Type	Name	Default Value	Description
31:16	RO	MJR	1h	Major Version Number
15:0	RO	MNR	400h	Minor Version Number

NOTE:

The PM9A3 supports NVM Express version 1.4.

[Table 127] Interrupt Mask Set

Bits	Type	Name	Default Value	Description
31:0	RW1S	IVMS	0h	Interrupt Vector Mask Set

[Table 128] Interrupt Mask Clear

Bits	Type	Name	Default Value	Description
31:00	RW1C	IVMC	0h	Interrupt Vector Mask Clear

[Table 129] Controller Configuration

Bits	Type	Name	Default Value	Description
31:24	RO	-	0h	Reserved
23:20	RW	IOCQES	0h	I/O Completion Queue Entry Size (Configured as a power of 2) (Should be set to 4 for a 16 byte entry size)
19:16	RW	IOSQES	0h	I/O Submission Queue Entry Size (Configured as a power of 2) (Should be set to 6 for a 64 byte entry size)
15:14	RW	SHN	0h	Shutdown Notification 0h: No notification 1h: Normal shutdown notification 2h: Abrupt shutdown notification 3h: Reserved CSTS.SHST indicates shutdown status.
13:11	RW	AMS	0h	Arbitration Mechanism Selected 0h: Round Robin No other values supported.
10:7	RW	MPS	0h	Memory Page Size MPS is $2^{(12+MPS)}$ Shall be within CAP.MPSMAX and CAP.MPSMIN ranges.
6:4	RW	CSS	0h	Command Set Selected 0h: NVM Command Set No other values supported
3:1	RO	-	0h	Reserved
0	RW	EN	0h	Enable When set to 1, controller shall process commands. When cleared to 0, controller shall not process commands. This field is subject to CSTS.RDY and CAP.TO restrictions.

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[Table 130] Controller Status

Bits	Type	Name	Default Value	Description
31:6	RO	-	0h	Reserved
5	RW	PP	0h	Processing Paused
4	RW1C	NSSRO	0h	NVM Subsystem Reset Occurred
3:2	RO	SHST	0h	Shutdown Status 0h: Normal operation, no shutdown requested 1h: Shutdown processing occurring 2h: Shutdown processing complete 3h: Reserved
1	RO	CFS	0h	Controller Fatal Status
0	RO	RDY	0h	1h: Controller ready to process commands 0h: Controller shall not process commands.

[Table 131] NVM Subsystem Reset

Bits	Type	Name	Default Value	Description
31:0	RW	NSSRC-	0h	NVM Subsystem Reset Control

[Table 132] Admin Queue Attributes

Bits	Type	Name	Default Value	Description
31:28	RO	-	0h	Reserved
27:16	RW	ACQS	0h	Admin Completion Queue Size Max: 4096 (Value of 4095h - 0's based value)
15:12	RO	-	0h	Reserved
11:0	RW	ASQS	0h	Admin Submission Queue Size Max: 4096 (Value of 4095h - 0's based value)

[Table 133] Admin Submission Queue Base Address

Bits	Type	Name	Default Value	Description
63:12	RW	ASQB	0h	Admin Submission Queue Base Address
11:0	RO	-	0h	Reserved

[Table 134] Admin Completion Queue Base Address

Bits	Type	Name	Default Value	Description
63:12	RW	ACQB	0h	Admin Completion Queue Base Address
11:0	RO	-	0h	Reserved

[Table 135] Submission Queue Tail y Doorbell

Bits	Type	Name	Default Value	Description
31:16	RO	-	0h	Reserved
15:0	RW	SQT	0h	Submission Queue Tail

[Table 136] Completion Queue Head y Doorbell

Bits	Type	Name	Default Value	Description
31:16	RO	-	0h	Reserved
15:0	RW	CQH	0h	Completion Queue Head

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6.0 SUPPORTED COMMAND SET

The Admin command sets and NVM I/O command sets of Samsung SSD PM9A3 are defined in compliant with NVM Express specification revision 1.4

6.1 Admin Command Set

The Admin command set is the commands that are submitted to the Admin Submission Queues. The detailed specifications are described in NVM Express specification document.

[Table 137] Opcode for Admin Commands

Opcode (Hex)	Command Name
00h	Delete I/O Submission Queue
01h	Create I/O Submission Queue
02h	Get Log Page
04h	Delete I/O Completion Queue
05h	Create I/O Completion Queue
06h	Identify
08h	Abort
09h	Set Feature
0Ah	Get Feature
0Ch	Asynchronous Event Request
0Dh	Namespace Management
10h	Firmware Commit
11h	Firmware Image Download
14h	Device Self-test
15h	Namespace Attachment
18h	Keep Alive (Not support)
19h	Directive Send
1Ah	Directive Receive
1Ch	Virtualization Management (Not support)
1Dh	NVMe-MI Send (Not support)
1Eh	NVMe-MI Receive (Not support)
7Ch	Doorbell Buffer Config (Not support)
80h - BFh	I/O Command Set Specific - B6h Get LBA Status (not support)
C0h - FFh	Vendor Specific

6.1.1 Identify Command

The Identify Command returns the data described below.

[Table 138] Identify Controller Data Structure

Bytes	O/M	Default Value	Description
1:0	M	144Dh	PCI Vendor ID
3:2	M	144Dh	PCI Subsystem Vendor ID
23:4	M	S#####	Serial Number(ASCII), # :Variables
63:24	M	SAMSUNG MZ1L2960HCJR-00A07 (960GB) SAMSUNG MZ1L21T9HCLS-00A07 (1920GB) SAMSUNG MZ1L23T8HBLA-00A07(3840GB)	Model Number (ASCII)
71:64	M	CS: NQxx MP : NAxx	Firmware Revision, #:Variables
72	M	2h	Recommended Arbitration Burst
75:73	M	002538h	IEEE OUI
76	O	0h	Multi-Interface Capabilities and Namespace Sharing Capability Bit 2: 1h - Controller is associated with an SR-IOV Virtual Function 0h - Controller is associated with a PCI Function. Bit 1: 1h - Device has Two or More controller 0h - Device has One Controller Bit 0: 1h - Device has Two or More physical PCI Express ports 0h - Device has One PCI Express port
77	M	9h	Maximum Data Transfer Size 9h: 2MB
79:78	M	06h	Controller ID (CNTLID)
83:80	M	0x10400	Controller Version
87:84	M	0x7A1200	RTD3 Resume Latency
91:88	M	0x7A1200	RTD3 Entry Latency
95:92	M	300h	Optional Asynchronous Events Supported (OAES)
99:96	M	80h	Controller Attributes (CTRATT) Bit 7 (Namespace Granularity): Reporting of Namespace Granulari
101:100	O	0h	Read Recovery Levels Supported (RRLS)
110:102	-	0h	Reserved
111	M	0h	Controller Type (CNTRLTYPE)
127:112	O		FRU Globally Unique Identifier (FGUID)
239:128		0h	Reserved
252:240	M	-	NVMe Management Interface Specification for Definition
253	M	1h	NVM Subsystem Report (NVMSR)
254	M	0h	VPD Write Cycle Information (VWCI)
255	M	1h	Management Endpoint Capabilities (MEC)

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257:256	M	5Fh	<p>Optional Admin Command Support Bits 15:10 are reserved.</p> <p>Bit 9 if set to '1', then the controller supports the Get LBA Status capability (refer to section 8.22). If cleared to '0', then the controller does not support the Get LBA Status capability.</p> <p>Bit 8 if set to '1', then the controller supports the Doorbell Buffer Config command. If cleared to '0', then the controller does not support the Doorbell Buffer Config command.</p> <p>Bit 7 if set to '1', then the controller supports the Virtualization Management command. If cleared to '0', then the controller does not support the Virtualization Management command.</p> <p>Bit 6 if set to '1', then the controller supports the NVMe-MI Send and NVMe-MI Receive commands. If cleared to '0', then the controller does not support the NVMe-MI Send and NVMe-MI Receive commands.</p> <p>Bit 5 if set to '1' then the controller supports Directives. If cleared to '0' then the controller does not support Directives. A controller that supports Directives shall support the Directive Send and Directive Receive commands. Refer to section 9.</p> <p>Bit 4 if set to '1' then the controller supports the Device Self-test command. If cleared to '0' then the controller does not support the Device Self-test command.</p> <p>Bit 3: 1h - Namespace Management and Namespace Attachment Commands Supported</p> <p>Bit 2: 1h – Firmware Activate/Download Supported</p> <p>Bit 1: 1h Format NVM Supported</p> <p>Bit 0: 1h Security Send and Security Receive Supported</p>
258	M	7h	<p>Abort Command Limit (Maximum number of concurrently outstanding Abort commands) (0's based value)</p>
259	M	3h	<p>Asynchronous Event Request Limit (Maximum number of concurrently outstanding Asynchronous Event Request commands) (0's based value)</p>
260	M	17h	<p>Firmware Updates Bits7:5-Reserved</p> <p>Bits4– 1h Controller supports firmware activation without a reset 0h Controller requires a reset for firmware to be activated Bits3:1– Number of firmware slots Bit 0 – 1h Slot 1 is read only</p>
261	M	Eh	<p>Log Page Attributes Bits 7:5 are reserved.</p> <p>Bit 4: Persistent Event log.</p> <p>Bit 3: the Telemetry Host-Initiated and Telemetry Controller-Initiated log pages and sending Telemetry Log Notices.</p> <p>Bit 2: extended data for the Get Log Page command.</p> <p>Bit 1: the Commands Supported and Effects log page.</p> <p>Bit 0: 0h SMART data is global for all namespaces</p>
262	M	3Fh	<p>Error Log Page Entries (Maximum number of Error Information log entries stored by controller) (0's based value)</p>
263	M	0h	<p>Number of Power States Support (0's based value)</p>
264	M	1h	<p>Admin Vendor Specific Command Configuration Bits 7:1 – reserved</p> <p>Bit 0 – Indicates Admin Vendor Specific Commands use the format defined in Admin and NVM Vendor Specific Commands (Optional) table of NVM Express spec.</p>
265	O	0h	Autonomous Power State Transition Attributes (APSTA)
267:266	M	15Eh	Warning Composite Temperature Threshold
269:268	M	166h	Critical Composite Temperature Threshold
271:270	O	0h	Maximum Time for Firmware Activation
275:272	O	0h	Host Memory Buffer Preferred Size
279:276	O	0h	Host Memory Buffer Minimum Size

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295:280	O	DF90356000h (960GB) 1BF1FC56000h (1920GB) 37E3EE56000h (3840GB)	Total NVM Capacity
311:296	O	0h	Unallocated NVM Capacity
315:312	O	0h	Replay Protected Memory Block Support(RPMBS)
317:316	O	23h	Extended Device Self-test Time (EDSTT)
318	O	1h	Device Self-test Options (DSTO)
319	M	0h	Firmware Update Granularity (FWUG)
321:320	M	0h	Keep Alive Support (KAS)
323:322	O	0h	Host Controlled Thermal Management Attributes (HCTMA)
325:324	O	0h	Minimum Thermal Management Temperature (MNTMT)
327:326	O	0h	Maximum Thermal Management Temperature (MXTMT)
331:328	O	3h	Sanitize Capabilities (SANICAP)
335:332	O	0h	Host Memory Buffer Minimum Descriptor Entry Size (HMMINDS)
337:336	O	0h	Host Memory Maximum Descriptors Entries (HMMAXD)
339:338	O	0h	NVM Set Identifier Maximum (NSECIDMAX) Non - IOD:0h, IOD:4h
341:340	O	0h	Endurance Group Identifier Maximum (ENDGIDMAX)
342	O	0h	ANA Transition Time (ANATT)
343	O	0h	Asymmetric Namespace Access Capabilities (ANACAP)
347:344	O	0h	ANA Group Identifier Maximum (ANAGRPMAX)
351:348	O	0h	Number of ANA Group Identifiers (NANAGRPID)
355:352	O	0h	Persistent Event Log Size (PELS)
511:356	-	-	Reserved
512	M	66h	Submission Queue Entry Size Bits 7:4 – 6h Max SQES (64 bytes) Bits 3:0 – 6h Required SQES (64 bytes)
513	M	44h	Completion Queue Entry Size Bits 7:4 – 4h Max SQES (16 bytes) Bits 3:0 – 4h Required SQES (16 bytes)
515:514	M	100h	Maximum Outstanding Commands (MAXCMD)
519:516	M	20h	Number of Namespaces
521:520	M	5Fh	Optional NVM Command Support Bits 15:8 - Reserved Bit 7 - 1h Verify command Supported 0h Not support Verify command Bit 6 - 1h Timestamp feature Supported 0h Not support the Timestamp feature Bit 5 – 1h Reservations Supported 0h Not support Reservations Bit 4 – 1h Save field in Set Feature & Select field in Get Feature Supported 0h Not support Save field in Set Feature & Select field in Get Feature Bit 3 – 1h Write Zeros Supported 0h Not support Write Zeros Bit 2 – 1h Dataset Management Supported 0h Not support Dataset Management Bit 1 – 1h Write Uncorrectable Supported 0h Not support Write Uncorrectable Bit 0 – 1h Compare Supported 0h Not support Compare
523:522	M	0h	Fused Operation Support Bits 15:1 – Reserved Bit 0 – 0h Compare/Write Fused Operation Not Supported
524	M	4h	Format NVM Attributes Bits 7:3 – Reserved Bit 2 – 1h Cryptographic Erase Bit 1 – 1h Secure Erase Per Namespace Bit 0 – 0h Format Per Namespace

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525	M	6h	Volatile Write Cache 0h – No VWC present
527:526	M	3FFh	Atomic Write Unit Normal
529:528	M	7h	Atomic Write Unit Power Fail (0's based value)
530	M	1h	NVM Vendor Specific Command Configuration Bits 7:1 – reserved Bit 0 – Indicates NVM Vendor Specific Commands use the format defined in NVM Express specification
531	M	0h	Reserved
533:532	O	0h	ACWU
535:534	M	0h	Reserved
539:536	O	0h	No SGL support
703:540	-	0h	Reserved
767:704		0h	Reserved
1023:768			NVM Subsystem NVMe Qualified Name (SUBNQN)
I/O Command Set Attributes			
1791:1024	-	0h	Reserved
2047:1792			Refer to the NVMe over Fabrics specification
Power State Descriptors			
2079:2048	M	Refer to 'Identify Power State Descriptor Data Structure'	Power State 0 Descriptor
3071:2080	O	0h	Power State 1 ~ 31 Descriptor (PSD1~N)
3072	O	3h	Error Mode Capabilities (ERRCAP)
3073	-	0h	Current Error Mode
3075:3074	O	136h	Supports Debugging Feature on Error Mode
3079:3076	O	0h	Reason for entering Error Mode.
3087:3080	O	LNUSRG39	Option ROM Version
3091:3088	O	2020/04/02	Option ROM Build Date
3092	O	1h	OEM Extended SMART Supported
3278:3093			Reserved
3279	M	6h	Security Features Supported
Vendor Specific			
4095:3280	-	-	Samsung Reserved

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[Table 139] Identify Power State Descriptor Data Structure

Bits	PS0	Description
255:184	0h	Reserved
183:182	2h	Active Power Scale(APS)
181:179	0h	Reserved
178:176	2h	Active Power Workload(APW)
175:160	339h	Active Power(ACTP)
159:152	0h	Reserved
151:150	2h	Idle Power Scale(IPS)
149:144	0h	Reservard
143:128	12Ch	Idle Power(IDLP)
127:125	0h	Reserved
124:120	0h	Relative Write Latency
119:117	0h	Reserved
116:112	0h	Relative Write Throughput
111:109	0h	Reserved
108:104	0h	Relative Read Latency
103:101	0h	Reserved
100:96	0h	Relative Read Throughput
95:64	46h	Exit Latency
63:32	46h	Entry Latency
31:26	0h	Reserved
25	0h	Non-Operational State
24	0h	Max Power Scale
23:16	0h	Reserved
15:00	339h	Maximum Power

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[Table 140] Identify Namespace Data Structure

Bytes	O/M	Default Value	Description
7:0	M	6FC81AB0h (960GB) DF8FE2B0h (1920GB) 1BF1F72B0h (3840GB)	Namespace Size(512B)
15:8	M	6FC81AB0h (960GB) DF8FE2B0h (1920GB) 1BF1F72B0h (3840GB)	Namespace Capacity(512B)
23:16	M	0h	Namespace Utilization A device may report Namespace Utilization equal to Namespace Capacity at all times if the product is not targeted for thin provisioning environments
24	M	12h	<p>Namespace Features Bits 7:5 are reserved.</p> <p>Bit 4 if set to '1' indicates that the fields NPWG, NPWA, NPDG, NPDA, and NOWS are defined for this namespace and should be used by the host for I/O optimization; and NOWS defined for this namespace shall adhere to Optimal Write Size field setting defined in NVM Sets Attributes Entry for the NVM Set with which this namespace is associated. If cleared to '0', the controller does not support the fields NPWG, NPWA, NPDG, NPDA, and NOWS for this namespace; and Optimal Write Size field in NVM Sets Attributes Entry for the NVM Set with which this namespace is associated should be used by the host for I/O optimization.</p> <p>Bit 3 if set to '1' indicates that the non-zero NGUID and non-zero EUI64 fields for this namespace are never reused by the controller. If cleared to '0', then the NGUID and EUI64 values may be reused by the controller for a new namespace created after this namespace is deleted. This bit shall be cleared to '0' if both NGUID and EUI64 fields are cleared to 0h. Refer to section 7.11.</p> <p>Bit 2 if set to '1' indicates that the controller supports the Deallocated or Unwritten Logical Block error for this namespace. If cleared to '0', then the controller does not support the Deallocated or Unwritten Logical Block error for this namespace. Refer to section 6.7.1.1.</p> <p>Bit 1 if set to '1' indicates that the fields NAWUN, NAWUPF, and NACWU are defined for this namespace and should be used by the host for this namespace instead of the AWUN, AWUPF, and ACWU fields in the Identify Controller data structure. If cleared to '0', then the controller does not support the fields NAWUN, NAWUPF, and NACWU for this namespace. In this case, the host should use the AWUN, AWUPF, and ACWU fields defined in the Identify Controller data structure in Figure 111. Refer to section 6.4.</p> <p>Bit 0 if set to '1' indicates that the namespace supports thin provisioning. Specifically, the Namespace Capacity reported may be less than the Namespace Size. When this feature is supported and the Dataset Management command is supported, then deallocated LBAs shall be reflected in the Namespace Utilization field. Bit 0 if cleared to '0' indicates that thin provisioning is not supported and the Namespace Size and Namespace Capacity fields report the same value.</p>
25	M	1h	Number of LBA Formats
26	M	0h	<p>Formatted LBA Size Bits 7:5 – Reserved</p> <p>Bit 4 – Metadata interleaved or separate (based on LBA format)</p> <p>Bit 3:0 – Indicates LBA format</p>
27	M	0h	<p>Metadata Capabilities Bits 7:2 – Reserved</p> <p>Bit 1 – Supports Metadata as separate buffer</p> <p>Bit 0 – Supports Metadata as extended LBA</p>
28	M	0h	<p>End-to-end Data Protection Capabilities Bits 7:5 – Reserved</p> <p>Bit 4 – Supports protection information as last 8 bytes of Metadata</p> <p>Bit 3 – Supports protection information as first 8 bytes of metadata</p> <p>Bit 2 – Supports Type 3 protection information</p> <p>Bit 1 – Supports Type 2 protection information</p> <p>Bit 0 – Supports Type 1 protection information</p>
29	M	0h	<p>End-to-End Data Protection Type Settings Bits 7:4 – Reserved</p> <p>Bit 3 – 1: Protection information transferred as first 8 bytes of metadata</p> <p>Bit 3 – 0: Protection information transferred as last 8 bytes of metadata</p> <p>Bit 2:0 – 000b: Protection information disabled</p> <p>Bit 2:0 – 1h: Protection type 1 enabled</p> <p>Bit 2:0 – 2h: Protection type 2 enabled</p> <p>Bit 2:0 – 3h: Protection type 3 enabled</p>

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30	O	0h	Namespace Multi-path I/O and Namespace sharing Capabilities (NMIC) Bits 7:1 - Reserved Bit 0 - 1 : Accessible by two or more controllers Bit 0 - 0 : Private namespace
31	O	0h	Reservation Capabilities (RESCAP) Bits 7 - Reserved Bits 6 - 1: Namespace supports the Exclusive Access (All Registrants reservation type) Bit 5 - 1 : Namespace supports the Write Exclusive (All Registrants reservation type) Bit 4 - 1 : Namespace supports the Exclusive Access (Registrants only reservation type) Bit 3 - 1 : Namespace supports the Write Exclusive (Registrants only reservation type) Bit 2 - 1 : Namespace supports the Exclusive Access Reservation type Bit 1 - 1 : Namespace supports the Write Exclusive Reservation type Bit 0 - 1 : Namespace supports the Persist Through Power Loss capability
32	O	80h	Format Progress Indicator(FPI)
33	O	9h	Deallocate Logical Block Features (DLFEAT)
35:34	O	3FFh	Namespace Atomic Write Unit Normal
37:36	O	7h	Namespace Atomic Write Unit Power Fail
39:38	O	0h	Namespace Atomic Compare & Write Unit
41:40	O	3FFh	Namespace Atomic Boundary Size Normal
43:42	O	0h	Namespace Atomic Boundary Offset
45:44	O	7h	Namespace Atomic Boundary Size Power Fail
47:46	O	0h	Namespace Optimal I/O Boundary (NOIOB)
63:48	O	DF90356000h (960GB) 1BF1FC56000h (1920GB) 37E3EE56000h (3840B)	NVM Capacity (NVMCAP)
65:64	O	FFh	Namespace Preferred Write Granularity (NPWG)
67:66	O	7h	Namespace Preferred Write Alignment (NPWA)
69:68	O	FFh	Namespace Preferred Deallocate Granularity (NPDG)
71:70	O	7h	Namespace Preferred Deallocate Alignment (NPDA)
73:72	O	FFh	Namespace Optimal Write Size (NOWS)
99:74	O	0h	Reserved
101:100	O	0h	NVM Set Identifier (NVMSETID)
103:102	O	0h	Endurance Group Identifier (ENDGID)
119:104	O	Update by Vendor Command	Namespace Globally Unique Identifier (NGUID) #:Variables *NGUID specifies data in a big endian format.
127:120	O	0h	IEEE Extended Unique Identifier(EUI64) #:Variables *EUI64 specifies data in a big endian format.
131:128	M	Refer to 'LBA Format 0 Data Structure'	LBA Format 0 Support
135:132	O	Refer to 'LBA Format 1 Data Structure'	LBA Format 1 Support
139:136	O	0h	LBA Format 2 Support
143:140	O	0h	LBA Format 3 Support
147:144	O	0h	LBA Format 4 Support (N/A)
...			
191:188	O	0h	LBA Format 15 Support (N/A)
383:192	-	0h	Reserved
Vendor Specific			
4095:384	-	-	Samsung Reserved

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[Table 141] LBA Format 0 Data Structure

Bits	Name	Default Value	Description
31:26	-	0h	Reserved
25:24	RP	0h	Relative Performance
23:16	LBADS	9h	LBA Data Size
15:00	MS	0h	Metadata Size

[Table 142] LBA Format 1 Data Structure

Bits	Name	Default Value	Description
31:26	-	0h	Reserved
25:24	RP	0h	Relative Performance
23:16	LBADS	Ch	LBA Data Size
15:00	MS	0h	Meta data Size

6.2 NVM Express I/O Command Set

[Table 143] Opcode for NVM Express I/O Commands

Opcode (Hex)	Command Name
00h	Flush
01h	Write
02h	Read
04h	Write Uncorrectable
05h	Compare
08h	Write Zeroes
09h	Dataset Management

NOTE:

1) Deallocate feature in Dataset Management command is only supported in the Samsung SSD PM9A3.

6.3 SMART/Health Information

[Table 144] SMART/Health Information Log

Bytes	Default Value	Attribute Description
0	0	Critical Warning Bit 7:5 – Reserved Bit 4 – 1h: the volatile memory backup device has failed. (only valid if the controller has a volatile memory backup solution) Bit 3 – 1h: the media has been placed in read only mode Bit 2 – 1h: the device reliability has been degraded due to significant media related errors or any internal error that degrades device reliability Bit 1 – 1h: the temperature has exceeded a critical threshold Bit 0 – 1h: the available spare space has fallen below the threshold
2:1	Current Temp	Temperature
3	100	Available Spare
4	10	Available Spare Threshold
5	0	Percentage Used
31:6	-	Reserved
47:32	0	Data Units Read
63:48	0	Data Units Written
79:64	0	Host Read Commands
95:80	0	Host Write Commands
111:96	0	Controller Busy Time
127:112	0	Power Cycles
143:128	0	Power On Hours
159:144	0	Unsafe Shutdowns
175:160	0	Media Errors
191:176	0	Number of Error Information Log Entries
195:192	0	Warning Composite Temperature Time
199:196	0	Critical Composite Temperature Time
201:200	Current Temp	Temperature Sensor 1
203:202	Current Temp	Temperature Sensor 2
205:204	-	Temperature Sensor 3
207:206	-	Temperature Sensor 4
209:208	-	Temperature Sensor 5
211:210	-	Temperature Sensor 6
213:212	-	Temperature Sensor 7
215:213	-	Temperature Sensor 8
511:216	-	Reserved

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6.4 Extended SMART Information

[Table 145] Extended SMART Information Log (LID : 0xCA)

Bytes	Default Value	Attribute Description
2:0	ABh	Lifetime Program Fail Cnt ID
4:3	64h	Lifetime Program Fail Cnt Normalized Value
11:5	0h	Lifetime Program Fail Cnt Current Raw Value
14:12	ACh	Lifetime Erase Fail Cnt ID
16:15	64h	Lifetime Erase Fail Cnt Normalized Value
23:17	0h	Lifetime Erase Fail Cnt Current Raw value
26:24	ADh	Lifetime Wearlevel Cnt ID
28:27	64h	Lifetime Wearlevel Cnt Normalized Value
		Lifetime Wearlevel Cnt Current Raw value
35:29	0h	Bytes 1-0: Min. erase cycles Bytes 3-2: Max. erase cycles Bytes 5-4: Avg. erase cycles
38:36	B8h	Lifetime E2E Error Cnt ID
40:39	64h	Lifetime E2E Error Cnt Normalized Value
47:41	0h	Lifetime E2E Error Cnt Current Raw Value
50:48	C7h	Lifetime CRC Error Cnt ID
52:51	64h	Lifetime CRC Error Cnt Normalized Value
59:53	0h	Lifetime CRC Error Cnt Current Raw Value
62:60	E2h	Media Wear Percentage ID
64:63	64h	Media Wear Percentag Normalized Value
71:65	0h	Media Wear Percentag Current Raw Value
74:72	E3h	Host Read Percentage ID
76:75	64h	Host Read Percentage Normalized Value
83:77	0h	Host Read Percentage Current Raw Value
86:84	E4h	Workload Timer ID
88:87	64h	Workload Timer Normalized Value
95:89	0h	Workload Timer Current Raw Value
98:96	EAh	Lifetime Thermal Throttle Status ID
100:99	64h	Lifetime Thermal Throttle Status Normalized Value
		Lifetime Thermal Throttle Status Current Raw Value Bytes 0: Throttle status reported as integer percentage.
107:101	64h	Bytes 1-4: Throttling event count. Number of times thermal throttle has activated. Preserved over power cycles. Byte 5: Reserved.
131:108	0	Reserved
134:132	F4h	Lifetime Physical Pages Written Cnt ID
136:135	64h	Lifetime Physical Pages Written Cnt Normalized Value
143:137	0h	Lifetime Physical Pages Written Cnt Current Raw Value
146:144	F5h	Lifetime Data Unit Written ID
148:147	64h	Lifetime Data Unit Written Normalized Value
155:149	0h	Lifetime Data Unit Written Current Raw Value
255:156	0h	Reserved
259:256	0h	Lifetime write amplification factor
263:260	0h	Trailing hour write amplification factor
279:264	0h	Lifetime user writes
295:280	0h	Lifetime NAND writes
311:296	0h	Lifetime user reads
315:312	0h	Lifetime retired block count

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317:316	Current Temperature	Current temperature
319:318	Cap health	Capacitor health
323:320	Lifetime Unused Reserved Block	Lifetime Unused Reserved Block
331:324	0h	Read Reclaim count
339:332	0h	Lifetime UECC count
343:340	0h	Lifetime Used Reserved Block
359:344	0h	Power on hours
375:360	0h	Lifetime clean shutdown count on power loss(NPO count)
391:376	0h	Lifetime unclean shutdowns on power loss(SPO count)
395:392	0h	Perf Indicator
399:396	0h	WearLevel Count
403:400	0h	HW Error Type
407:404	0h	DeviceFail Recovery Count (Incomplete Shutdown)
411:408	0h	SRAM CECC Count (CoreSRAM)
415:412	0h	SRAM CECC Address (CoreSRAM)
419:416	0h	SRAM CECC Count (Buffer)
423:420	0h	SRAM CECC Address (Buffer)
427:424	0h	DRAM CECC Count
435:428	0h	DRAM CECC Address
439:436	0h	DRAM UECC Count
447:440	0h	DRAM UECC Address
451:448	0h	E2E Error Count
453:452	0h	FW Update Success Count
455:454	0h	FW Update Fail Count
459:456	Highest temperature	Highest Temperature
463:460	Lowest Temperature	Lowest Temperature
471:464	0h	Read Recovery Attempts
479:472	0h	Reset Count
495:480	0h	Trimmed Sector Count
499:496	0h	Security Meta Erase Fail Count
503:500	0h	Over Temperature Count
507:504	0h	Under Temperature Count
511:508	0h	Recovery Reset Count

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[Table 146] Enhanced SMART Log (LID : 0xC4)

Bytes	Default Value	Attribute Description
1:0	0h	Throughput Performance
2	0h	Timed Workload Media Wear
3	0h	Times Workload Host Read/Write Ratio
5:4	0h	Read Error Rate
7:6	0h	Write Error Rate
11:8	0h	Unrecoverable Write Errors
15:12	0h	Read Recovery Attempts
17:16	Temperature	Average Short Term Temperature
19:18	Temperature	Average Long Term Temperature
21:20	Temperature	Highest Temperature
23:22	Temperature	Lowest Temperature
25:24	Temperature	Highest Average Short Term Temperature
27:26	Temperature	Lowest Average Short Term Temperature
29:28	Temperature	Highest Average Long Term Temperature
31:30	Temperature	Lowest Average Long Term Temperature
33:32	15Eh	Specified Maximum Operating Temperature
35:34	111h	Specified Minimum Operating Temperature
39:36	0h	Time in Over Temperature in Minutes
55:40	0h	Physical Media Units Written
71:56	0h	Physical Media Units Read
77:72	0h	Bad User NAND block count (Raw)
79:78	64h	Bad User NAND block count (Normalized)
85:80	0h	Bad System NAND block count (Raw)
87:86	64h	Bad System NAND block count (Normalized)
91:88	0h	End to End Correction Counts (Detected Errors)
95:92	0h	End to End Correction Counts (Corrected Errors)
96:96	0h	System data % used
97:97	64h	% Free Blocks
105:98	0h	Unaligned I/O
113:106	0h	Security Version Number
121:114	0h	NUSE
137:122	0h	PLP Start Count
153:138	Capacity specific	Endurance Estimate
157:154	0h	BAD TLP Count
161:158	0h	BAD DLLP Count
165:162	0h	PHY Error Count
169:166	0h	Thermal Protection Count
173:170	0h	Thermal Shutdown Count
511:174	0h	Reserved

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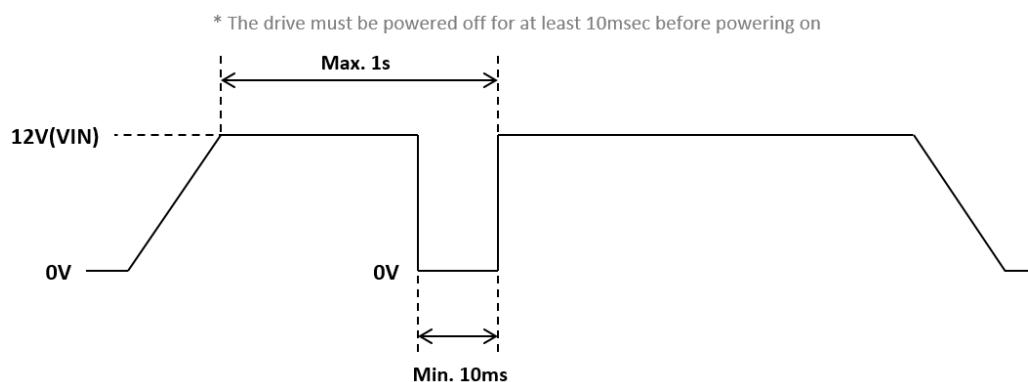
7.0 SPOR Specification (Sudden Power Off and Recovery)

7.1 Data Recovery in Sudden Power off

If power interruption is detected, SSD dumps all cached user data and meta data to NAND Flash. SSD could protect even the user data in DRAM from sudden power off while SSD is used with cache on. Commonly, data is protected all of the operation period.

7.2 Minimum Off time

In sudden power off case, minimum 10ms off time is required for stability



7.3 Time to Ready Sequence

In normal power-off recovery status, SSD needs less than 8 seconds to reach operating mode where SSD works perfectly with cache-on state. SSD is ready to respond identify Device command during FTL OPEN. When the sudden power-off occurs, the user data in DRAM will be dumped into the NAND Flash using the stored power in the capacitor. In sudden power-off recovery condition, mapping data will be loaded or the FTL meta data be rebuilt perfectly for initial max. 10 seconds. During this period, Identify Device command is still supported. It is called SPOR. (Sudden Power Off and Recovery)

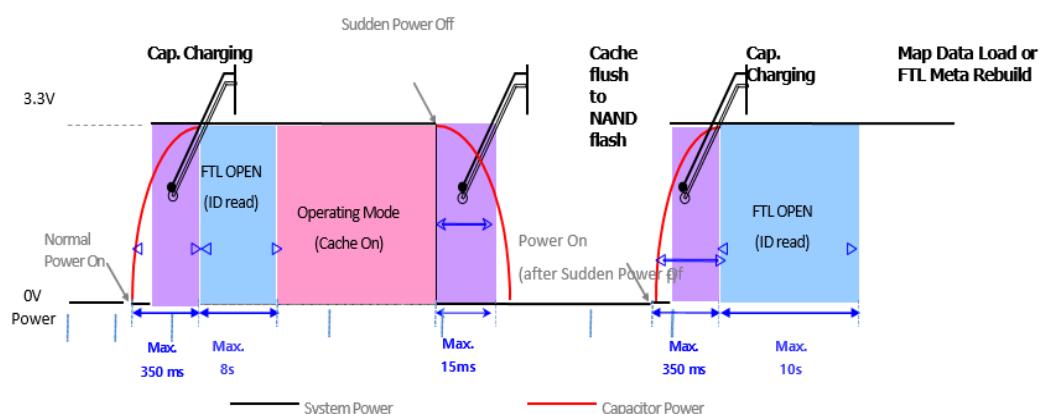


Figure 3. Sudden Power on-off operation

[Table 147] Device Ready Time for Normal Read / Write Operation after Sudden Power Off

	960GB	1920GB	3840GB
Open Time (sec)	10s	10s	20s

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8.0 UEFI EXPANSION ROM

The expansion ROM integrated in Samsung SSD PM9A3 supports booting UEFI operating system

8.1 Supported Operating Systems

Index	Operating Systems bootable on PM9A3 drive
1	RHEL 7.2 (Kernel 3.10.327)
2	RHEL 7.6 (Kernel 3.10.957)
3	CentOS 7.3 (Kernel 3.10.0-514)
4	CentOS 7.6 (Kernel 3.10.0-957)
5	Ubuntu 16.10 (Kernel 4.08)
6	Ubuntu 18.10 (Kernel 4.18)
7	Windows server 2016
8	Windows server 2019

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9.0 PRODUCT COMPLIANCE

9.1 Product regulatory compliance and Certifications

[Table 148] Certifications and Declarations

Category	Certifications
Safety	c-UL-us
	CE
	TUV
	CB
EMC	CE (EU)
	BSMI (Taiwan)
	KC (South Korea)
	VCCI (Japan)
	RCM (Australia)
	FCC (USA)
	IC (CANADA)

The three existing compliance marks (C-Tick, A-Tick and RCM) are consolidated into a single compliance mark - the RCM.



Caution: Any changes or modifications in construction of this device which are not expressly approved by the party responsible for compliance could void the user's authority to operate the equipment.

NOTE: This equipment has been tested and found to comply with the limits for a Class B digital device, pursuant to part 15 of the FCC Rules. These limits are designed to provide reasonable protection against harmful interference in a residential installation. This equipment generates, uses and can radiate radio frequency energy and, if not installed and used in accordance with the instructions, may cause harmful interference to radio communications. However, there is no guarantee that interference will not occur in a particular installation. If this equipment does cause harmful interference to radio or television reception, which can be determined by turning the equipment off and on, the user is encouraged to try to correct the interference by one or more of the following measures:

- Reorient or relocate the receiving antenna.
- Increase the separation between the equipment and receiver.
- Connect the equipment into an outlet on a circuit different from that to which the receiver is connected.
- Consult the dealer or an experienced radio/TV technician for help.

Modifications not expressly approved by the manufacturer could void the user's authority to operate the equipment under FCC rules.



1. 기자재 명칭 : SSD (Solid State Drive)
2. 모델명(Model): 라벨 별도 표기
3. 제조연월 : 라벨 별도 표기
4. 제조사 : 삼성전자(주)
5. 제조국가 : 대한민국
6. 상호명 : 삼성전자(주)

Industry Canada ICES-003 Compliance Label:
CAN ICES-3 (B)/NMB-3(B)

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10.0 References

[Table 149] Standards References

Item	Website
PCI Express Base Specification Revision 3.1	http://www.pcisig.com/specifications/pciexpress/base3/
PCI Express CEM Specification Revision 3.0	http://www.pcisig.com/specifications/
NVM Express Specification Rev. 1.4	http://www.nvme.org/
NVM Express Management Interface, Revision 1.1a	http://www.nvme.org/
Enterprise SSD Form Factor Version 1.0a	http://www.ssdformfactor.org/
Solid-State Drive Requirements and Endurance Test Method (JESD218A)	http://www.jedec.org/standards-documents/docs/jesd218a
Solid-State Drive Requirements and Endurance Test Method (JESD219A)	http://www.jedec.org/standards-documents/docs/jesd219a

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